OPAx202 精密、低噪声、高电容驱动能力 36V 运算放大器

1 特性

- 精密超级 ß 性能：
  - 低失调电压：200µV（最大值）
  - 超低温漂：1µV/°C（最大值）
- 出色的效率：
  - 静态电流：580µA（典型值）
  - 增益带宽积：1MHz
  - 低输入电压噪声：9nV/√Hz
- 方便易用，简化设计：
  - 高容性负载驱动：25nF 负载时具有 5µs 稳定时间
  - 超高输入阻抗：3000GΩ 和 0.5pF
  - 抗电磁干扰 (EMI)，具有过热保护和短路保护
- 稳定性能：
  - 高 CMRR 和 A_{OL}：126dB（最小值）
  - 高 PSRR：126dB（最小值）
- 低偏置电流：2nA（最大值）
- 0.1Hz 至 10Hz 低噪声：$0.2\mu V_{PP}$
- 宽电源电压：±2.25V 至 ±18V
- 取代 OP-07 和 OP-27

2 应用

- 数据采集 (DAQ)
- 实验室和现场仪表
- 商用网络和服务器 PSU
- 多参数患者监护仪
- 串式逆变器

3 说明

OPA202、OPA2202 和 OPA4202 (OPAx202) 是在 TI 业界领先的精密超级 ß 互补双极半导体工艺基础上构建的一系列器件。此工艺提供超低闪烁噪声、低失调电压、低失调电压温漂和优异线性度，并具有共模和电源变化。这些器件具有一系列出色的特性：直流精度、高容性负载驱动以及外部 EMI 保护、过热保护和短路保护。

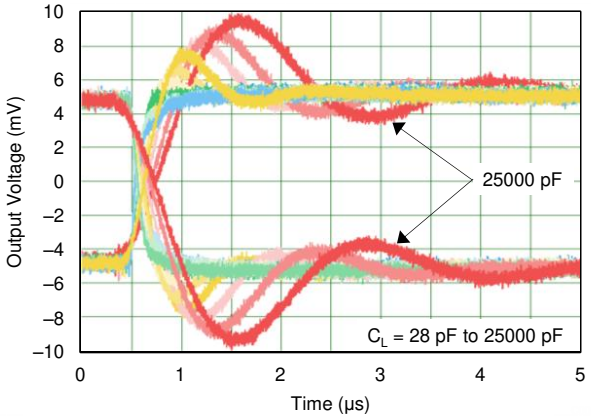
±18V 时的电源电流为 580µA。OPAx202 系列不会出现相位反转，并能够在高容性负载下保持稳定。OPAx202 额定工作温度范围为 -40°C 至 +105°C。

器件信息(1)

器件型号	封装	封装尺寸（标称值）
OPA202	SOIC (8)	4.90mm × 3.91mm
	SOT-23 (5)	2.90mm × 1.60mm
	VSSOP (8)（预览）	3.00mm × 3.00mm
OPA2202	VSSOP (8)	3.00mm × 3.00mm
OPA4202	SOIC (14)	8.65mm × 3.91mm

(1) 如需了解所有可用封装，请参阅数据表末尾的封装选项附录。

OPAx202 即使在直接驱动高容性负载时也表现优异



本文档旨在为方便起见，提供有关 TI 产品中文版本的信息，以确认产品的概要。 有关适用的官方英文版本的最新信息，请访问 www.ti.com，其内容始终优先。 TI 不保证翻译的准确性和有效性。 在实际设计之前，请务必参考最新版本的英文版本。

目录

1 特性 ... 1
2 应用 ... 1
3 说明 ... 1
4 修订历史记录 ... 2
5 Pin Configuration and Functions ... 3
6 Specifications ... 6
6.1 Absolute Maximum Ratings ... 6
6.2 ESD Ratings ... 6
6.3 Recommended Operating Conditions ... 6
6.4 Thermal Information: OPA202 ... 7
6.5 Thermal Information: OPA2202 ... 7
6.6 Thermal Information: OPA4202 ... 7
6.7 Electrical Characteristics ... 8
6.8 Typical Characteristics ... 10
6.9 Typical Characteristics ... 11
7 Detailed Description ... 18
7.1 Overview ... 18
7.2 Functional Block Diagram ... 18
7.3 Feature Description ... 19
7.4 Device Functional Modes ... 25
8 Application and Implementation ... 26
8.1 Application Information ... 26
8.2 Typical Application ... 28
9 Power Supply Recommendations ... 29
10 Layout ... 30
10.1 Layout Guidelines ... 30
10.2 Layout Example ... 30
11 器件和文档支持 ... 31
11.1 器件支持 ... 31
11.2 文档支持 ... 31
11.3 相关链接 ... 32
11.4 接收文档更新通知 ... 32
11.5 支持资源 ... 32
11.6 商标 ... 32
11.7 静电放电警告 ... 32
11.8 Glossary ... 32
12 机械、封装和可订购信息 ... 32

4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Revision D (December 2019) to Revision E — **Page**

- 已添加 向数据表添加了 OPA202 8 引脚 VSSOP (DGK) 预发布封装和相关内容 ... 1

Changes from Revision C (October 2018) to Revision D — **Page**

- 已更改 将 OPA2202 和 OPA4202 器件从预告信息（预发布）更改为生产数据（正在供货） ... 1

Changes from Revision B (December 2018) to Revision C — **Page**

- 已添加 向数据表添加了 OPA2202 和 OPA4202 预发布器件和相关内容 ... 1
- 已删除 *Operating Voltage* section; redundant information ... 19

Changes from Revision A (September 2018) to Revision B — **Page**

- 已更改 将 SOT-23 封装从预发布更改为生产数据 ... 1

Changes from Original (October 2017) to Revision A — **Page**

- 已添加 添加了适用于 SOT-23 封装产品的预发布内容 ... 1

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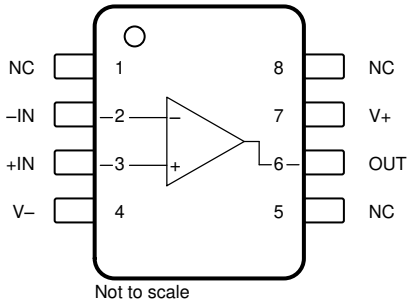
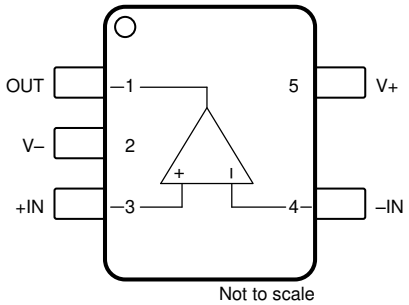
5 Pin Configuration and Functions

OPA202 D, DGK(1) Packages
8-Pin SOIC and VSSOP
Top View



OPA202 DBV Package
5-Pin SOT-23
Top View



(1) DGK package is preview.

Pin Functions: OPA202

PIN			I/O	DESCRIPTION
NAME	NO.			
	D (SOIC) DGK (VSSOP)	DBV (SOT-23)		
–IN	2	4	I	Inverting input
+IN	3	3	I	Noninverting input
NC	1, 5, 8	—	—	No internal connection (can be left floating)
OUT	6	1	O	Output
V–	4	2	—	Negative (lowest) power supply
V+	7	5	—	Positive (highest) power supply

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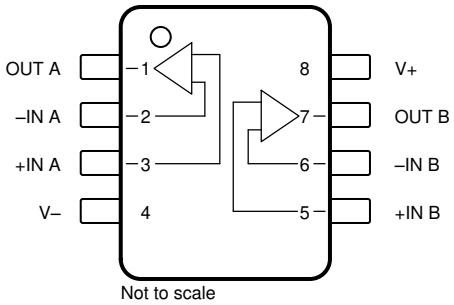
OPA2202 DGK Package
8-Pin VSSOP
Top View



Not to scale

Pin Functions: OPA2202

PIN		I/O	DESCRIPTION
NAME	NO.		
–IN A	2	I	Inverting input channel A
+IN A	3	I	Noninverting input channel A
–IN B	6	I	Inverting input channel B
+IN B	5	I	Noninverting input channel B
OUT A	1	O	Output channel A
OUT B	7	O	Output channel B
V–	4	—	Negative supply
V+	8	—	Positive supply

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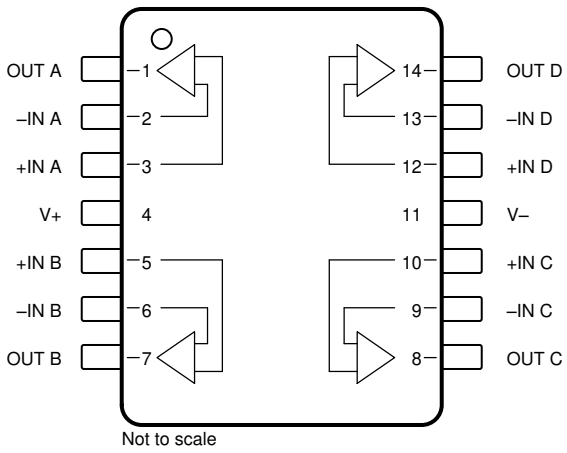
OPA4202 D Package
14-Pin SOIC
Top View



Not to scale

Pin Functions: OPA4202

PIN		I/O	DESCRIPTION
NAME	NO.		
–IN A	2	I	Inverting input channel A
+IN A	3	I	Noninverting input channel A
–IN B	6	I	Inverting input channel B
+IN B	5	I	Noninverting input channel B
–IN C	9	I	Inverting input channel C
+IN C	10	I	Noninverting input channel C
–IN D	13	I	Inverting input channel D
+IN D	12	I	Noninverting input channel D
OUT A	1	O	Output channel A
OUT B	7	O	Output channel B
OUT C	8	O	Output channel C
OUT D	14	O	Output channel D
V–	11	—	Negative supply
V+	4	—	Positive supply

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6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
Supply voltage, V_S = (V+) – (V–)	Single-supply			40	V
	Dual-supply			±20	
Signal input pins	Voltage	Common-mode(2)	(V–) – 0.5	(V+) + 0.5	
		Differential(3)		±0.5	
	Current			±10	mA
Output short current(4)			Continuous		
Operating temperature, T_A			–40	125	°C
Junction temperature, T_J				125	
Storage temperature, T_{stg}			–65	150	

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) Input terminals are diode-clamped to the power-supply rails. Input signals that swing more than 0.5 V beyond the supply rails must be current-limited to 10 mA or less.
(3) Input terminals are anti-parallel diode-clamped to each other. Input signals that cause differential voltages of swing more than ± 0.5 V must be current-limited to 10 mA or less.
(4) Short-circuit to ground, one amplifier per package.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2500	V
		Charged device model (CDM), per JEDEC specification JESD22-C101(2)	±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V_S	Supply voltage, [(V+) – (V–)]	Single-supply	4.5		36	V
		Dual-supply	±2.25		±18	
T_A	Specified temperature		–40		105	°C

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6.4 Thermal Information: OPA202

THERMAL METRIC(1)		OPA202			UNIT
		D (SOIC)	DGK (VSSOP)	DBV (SOT-23)	
		8 PINS	8 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	136	176.7	206.0	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	74	63.9	121.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	62	99.4	65.9	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	19.7	8.8	39.0	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	54.8	97.6	65.6	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

6.5 Thermal Information: OPA2202

THERMAL METRIC(1)		OPA2202	UNIT
		DGK (VSSOP)	
		8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	180.1	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	68.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	101.4	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	10.5	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	99.8	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

6.6 Thermal Information: OPA4202

THERMAL METRIC(1)		OPA4202	UNIT
		D (SOIC)	
		14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	87.9	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	42.7	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	44.6	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	8.9	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	44.1	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

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6.7 Electrical Characteristics

at T_A = 25°C, V_S = ±18 V, V_{CM} = V_S / 2, and V_{OUT} = V_S / 2, R_L = 10 kΩ connected to V_S / 2 (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
OFFSET VOLTAGE							
V_{OS}	Input offset voltage	V_S = ±18 V			±20	±200	µV
		V_S = ±18 V, T_A = –40°C to +105°C				±250	
dV_{OS}/dT	Input offset voltage drift	OPA202, OPA4202ID	T_A = –40°C to +105°C		±0.5	±1	µV/°C
		OPA2202IDGK	T_A = –40°C to +105°C		±0.5	±1.5	µV/°C
PSRR	Input offset voltage versus power supply	V_S = ±2.25 V to ±18 V			±0.1	±0.5	µV/V
		V_S = ±2.25 V to ±18 V, T_A = –40°C to +105°C				±0.5	
INPUT BIAS CURRENT							
I_B	Input bias current				±0.25	±2	nA
		T_A = –40°C to +105°C				±2.1	
I_{OS}	Input offset current	OPA202			±15	±150	pA
			T_A = –40°C to +105°C			±700	
		OPA2202IDGK, OPA4202ID			±25	±250	
			T_A = –40°C to +105°C			±700	
NOISE							
	Input voltage noise	f = 0.1 Hz to 10 Hz			0.2		$µV_{PP}$
					0.03		$µV_{RMS}$
e_n	Input voltage noise density	f = 10 Hz			9.5		nV/√Hz
		f = 100 Hz			9.1		
		f = 1 kHz			9		
i_n	Input current noise	f = 1 kHz			0.076		pA/√Hz
INPUT VOLTAGE RANGE							
V_{CM}	Common-mode voltage range			(V–) + 1.5		(V+) – 1.5	V
CMRR	Common-mode rejection ratio	V_S = ±2.25 V	(V–) + 1.5 V < V_{CM} < (V+) – 1.5 V	114	131		dB
			(V–) + 1.5 V < V_{CM} < (V+) – 1.5 V, T_A = –40°C to +105°C	114			
		V_S = ±18 V	(V–) + 1.5 V < V_{CM} < (V+) – 1.5 V	126	148		
			(V–) + 1.5 V < V_{CM} < (V+) – 1.5 V, T_A = –40°C to +105°C	119			
INPUT CAPACITANCE							
	Differential				10 || 3.3		MΩ || pF
	Common-mode				3 || 0.5		TΩ || pF
OPEN-LOOP GAIN							
A_{OL}	Open-loop voltage gain	V_S = ±2.25 V	(V–) + 1.25 V ≤ V_O ≤ (V+) – 1.25 V, R_L = 10 kΩ	120	135		dB
			(V–) + 1.25 V ≤ V_O ≤ (V+) – 1.25 V, R_L = 10 kΩ, T_A = –40℃ to +105℃	119			
		V_S = ±18 V	(V–) + 1.25 V ≤ V_O ≤ (V+) – 1.25 V, R_L = 10 kΩ	126	150		
			(V–) + 1.25 V ≤ V_O ≤ (V+) – 1.25 V, R_L = 10 kΩ, T_A = –40℃ to +105℃	126			
		V_S = ±2.25 V	(V–) + 1.25 V ≤ V_O ≤ (V+) – 1.25 V, R_L = 2 kΩ	120	133		
			(V–) + 1.25 V ≤ V_O ≤ (V+) – 1.25 V, R_L = 2 kΩ, T_A = –40℃ to +105℃	119			
		V_S = ±18 V	(V–) + 1.25 V ≤ V_O ≤ (V+) – 1.25 V, R_L = 2 kΩ	126	150		
			(V–) + 1.25 V ≤ V_O ≤ (V+) – 1.25 V, R_L = 2 kΩ, T_A = –40℃ to +105℃	126			

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Electrical Characteristics (continued)

at T_A = 25°C, V_S = ±18 V, V_{CM} = V_S / 2, and V_{OUT} = V_S / 2, R_L = 10 kΩ connected to V_S / 2 (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
FREQUENCY RESPONSE							
GBW	Gain-bandwidth product				1		MHz
SR	Slew rate	10-V step, G = 1			0.35		V/µs
t_S	Settling time	To 0.1%, 10-V step , G = 1			30		µs
		To 0.01%, 10-V step , G = 1			32		
	Overload recovery time	V_{IN} × gain > V_S			4		µs
THD+N	Total harmonic distortion + noise	V_O = 3 V_{RMS}, G = 1, f = 1 kHz, R_L = 10 kΩ			0.0002%		
OUTPUT							
	Voltage output swing from rail	V_S = ±18 V	T_A = 25°C, No Load		650	750	mV
			T_A = 25°C, R_L = 10 kΩ		800	900	
			T_A = 25°C, R_L = 2 kΩ		1.05	1.15	V
			T_A = –40°C to +105°C, R_L = 10 kΩ			1	
			A_{OL} > 120 dB, R_L = 10 kΩ			1.05	
			A_{OL} > 120 dB, R_L = 2 kΩ			1.25	
I_{SC}	Short-circuit current	Sinking			35		mA
		Sourcing			35		
C_{LOAD}	Capacitive load drive				图 28		
Z_O	Open-loop output impedance	I_O = 0 mA, f = 1 MHz; see 图 27			50		Ω
POWER SUPPLY							
I_Q	Quiescent current per amplifier	I_O = 0 mA			580	800	µA
		I_O = 0 mA, T_A = –40°C to +105°C				900	

6.8 Typical Characteristics

表 1. Table of Graphs

DESCRIPTION	FIGURE
Offset Voltage Production Distribution	图 1
Offset Voltage Drift Distribution From –40°C to +105°C	图 2
Input Bias Current Production Distribution	图 3
Input Offset Current Production Distribution	图 4
Offset Voltage vs Temperature	图 5
Offset Voltage vs Common-Mode Voltage	图 6
Offset Voltage vs Supply Voltage	图 7
Open-Loop Gain and Phase vs Frequency	图 8
Closed-Loop Gain vs Frequency	图 9
Input Bias Current vs Common-Mode Voltage	图 10
Input Bias Current and Offset vs Temperature	图 11
Output Voltage Swing vs Output Current	图 12
Output Voltage Swing vs Output Current (Sourcing)	图 13
Output Voltage Swing vs Output Current (Sinking)	图 14
CMRR and PSRR vs Frequency	图 15
CMRR vs Temperature	图 16
PSRR vs Temperature	图 17
0.1-Hz to 10-Hz Voltage Noise	图 18
Input Voltage Noise Spectral Density vs Frequency	图 19
THD+N Ratio vs Frequency	图 20
THD+N vs Output Amplitude	图 21
Quiescent Current vs Supply Voltage	图 22
Quiescent Current vs Temperature	图 23
Open-Loop Gain vs Temperature (10-kΩ)	图 24
Open-Loop Gain vs Output Voltage Swing to Supply	图 25, 图 26
Open-Loop Output Impedance vs Frequency	图 27
Small-Signal Overshoot vs Capacitive Load (10-mV Step)	图 28
No Phase Reversal	图 29
Positive Overload Recovery	图 30
Negative Overload Recovery	图 31
Small-Signal Step Response (10-mV Step)	图 32, 图 33
Large-Signal Step Response (10-V Step)	图 34, 图 35
Settling Time (10-V Step)	图 36
Short-Circuit Current vs Temperature	图 37
Maximum Output Voltage vs Frequency	图 38
EMIRR vs Frequency	图 39

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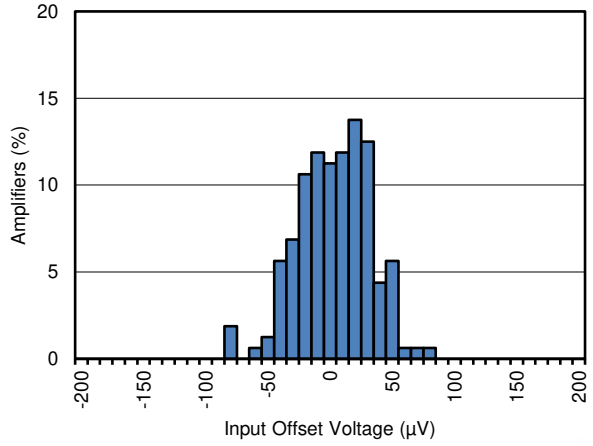
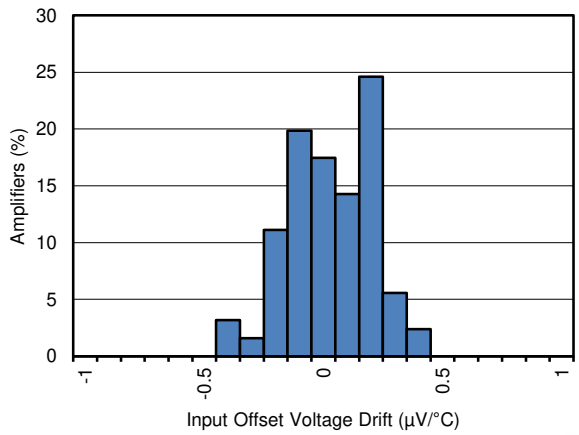
6.9 Typical Characteristics

at T_A = 25°C, V_S = ±18 V, V_{CM} = V_S / 2, R_{LOAD} = 10 kΩ connected to V_S / 2, and C_L = 100 pF (unless otherwise noted)



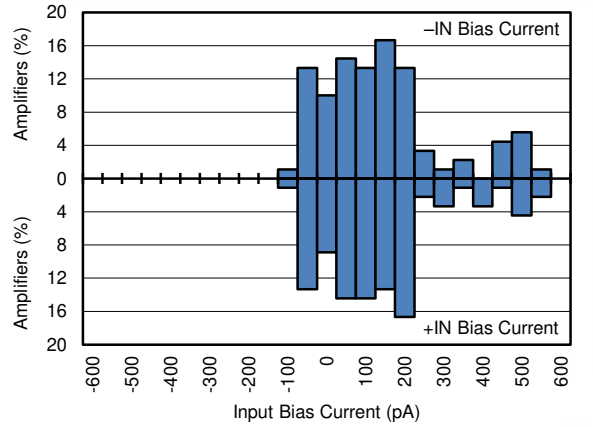
µ = –3.56 µV σ = 32.09 µV N = 252

图 1. Offset Voltage Production Distribution



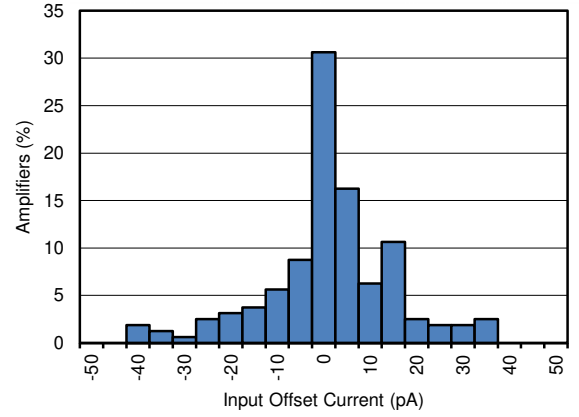
µ = –18.23 nV/°C σ = 177.41 nV/°C N = 252
T_A = –40°C to +105°C

图 2. Offset Voltage Drift Distribution



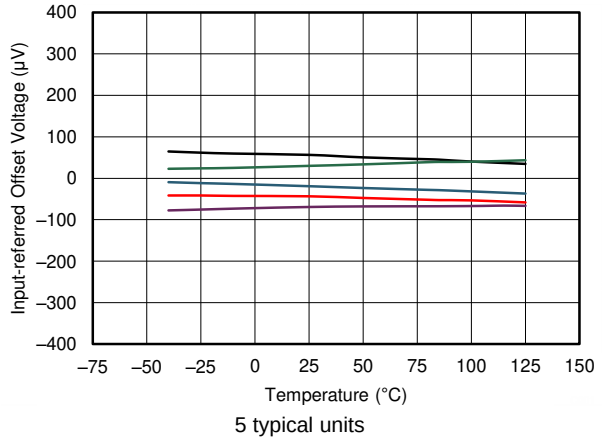
μ_{-IN} = 112.335 pA σ_{-IN} = 154.946 pA N = 90
μ_{+IN} = 112.448 pA σ_{+IN} = 152.739 pA

图 3. Input Bias Current Production Distribution



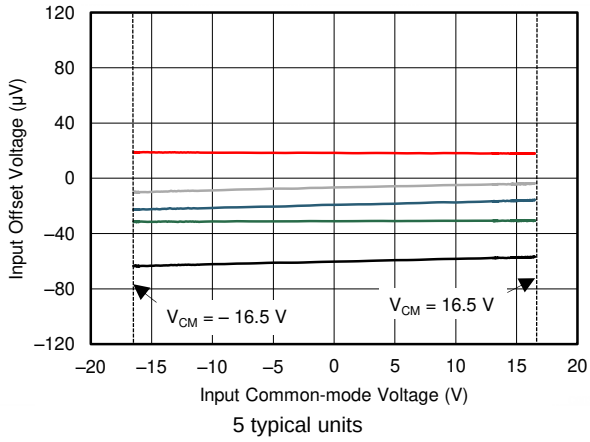
µ = 0.112 pA σ = 15.023 pA N = 90

图 4. Input Offset Current Production Distribution



5 typical units

图 5. Offset Voltage vs Temperature



5 typical units

图 6. Offset Voltage vs Common-Mode Voltage

Typical Characteristics (接下页)

at T_A = 25°C, V_S = ±18 V, V_{CM} = V_S / 2, R_{LOAD} = 10 kΩ connected to V_S / 2, and C_L = 100 pF (unless otherwise noted)

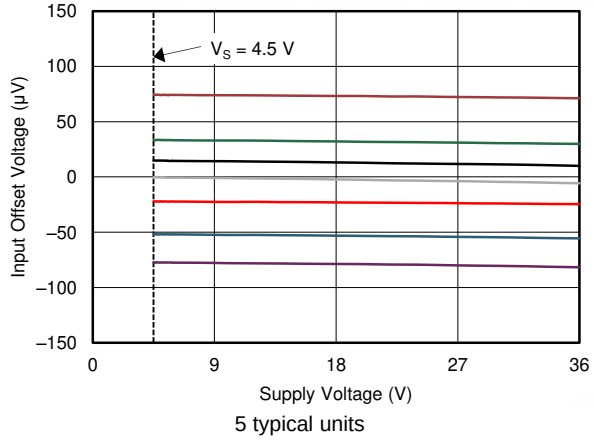


图 7. Offset Voltage vs Supply Voltage

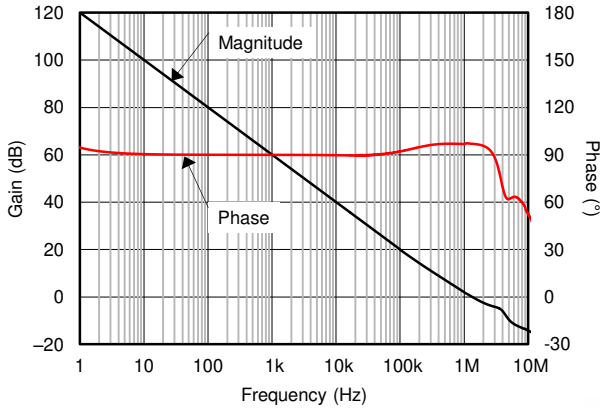


图 8. Open-Loop Gain and Phase vs Frequency

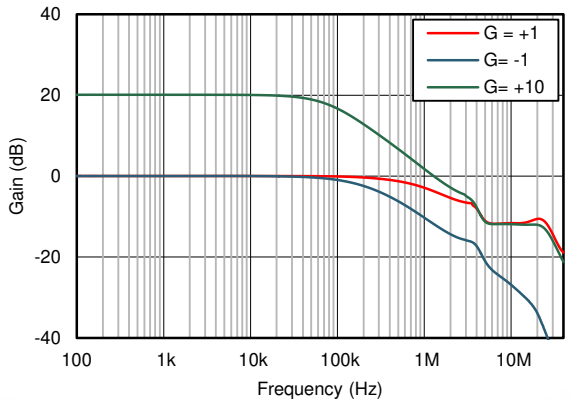


图 9. Closed-Loop Gain vs Frequency

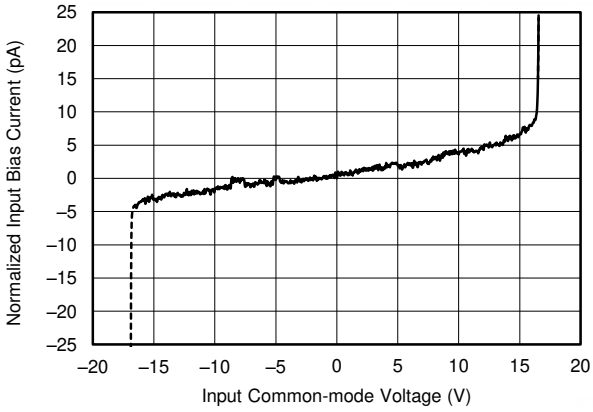


图 10. Input Bias Current vs Common-Mode Voltage

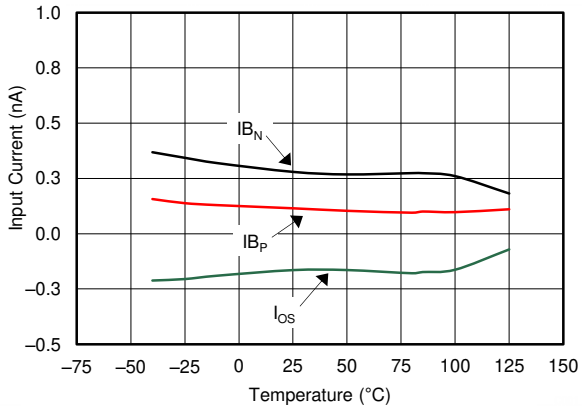


图 11. Input Bias Current and Offset vs Temperature

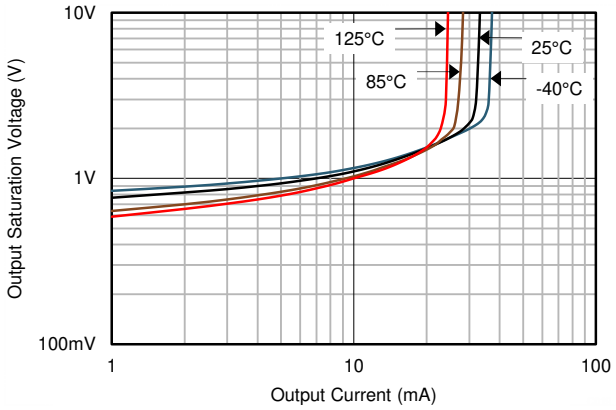


图 12. Output Voltage Swing vs Output Current

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Typical Characteristics (接下页)

at T_A = 25°C, V_S = ±18 V, V_{CM} = V_S / 2, R_{LOAD} = 10 kΩ connected to V_S / 2, and C_L = 100 pF (unless otherwise noted)

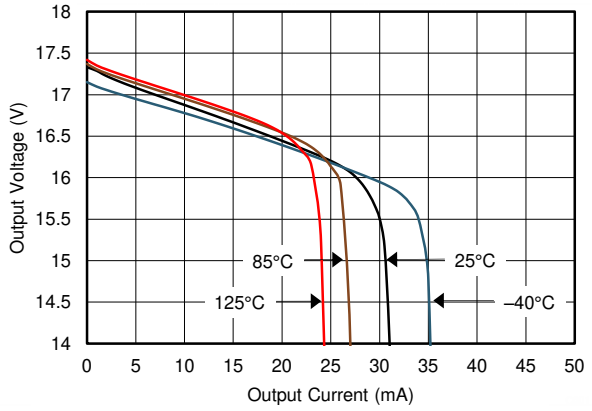


图 13. Output Voltage Swing vs Output Current (Sourcing)

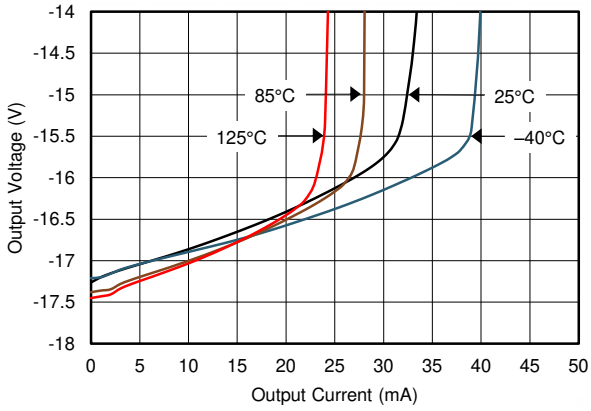


图 14. Output Voltage Swing vs Output Current (Sinking)

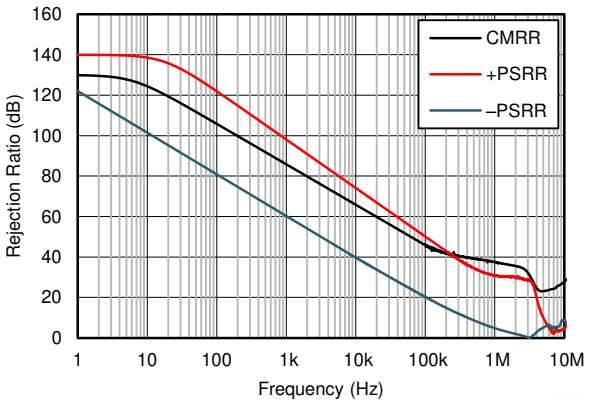


图 15. CMRR and PSRR vs Frequency

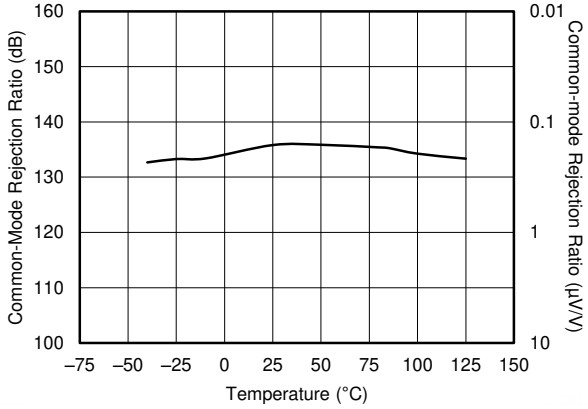


图 16. CMRR vs Temperature

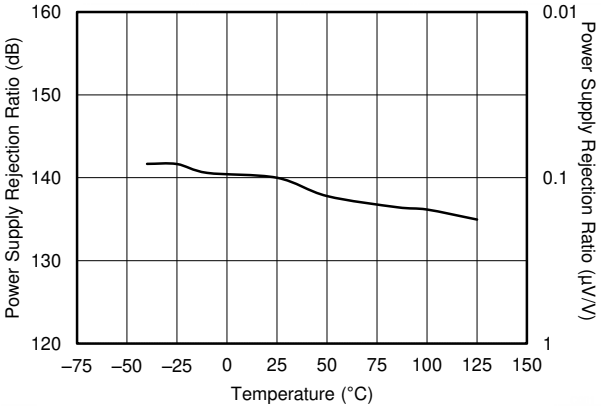


图 17. PSRR vs Temperature

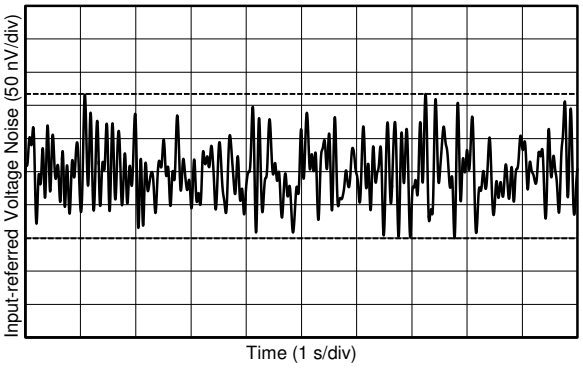


图 18. 0.1-Hz to 10-Hz Voltage Noise

Typical Characteristics (接下页)

at T_A = 25°C, V_S = ±18 V, V_{CM} = V_S / 2, R_{LOAD} = 10 kΩ connected to V_S / 2, and C_L = 100 pF (unless otherwise noted)

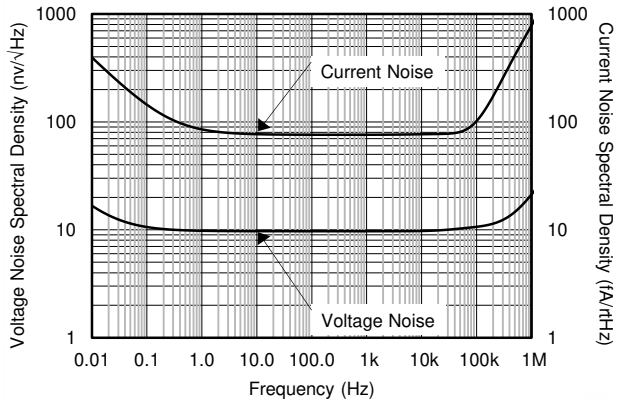
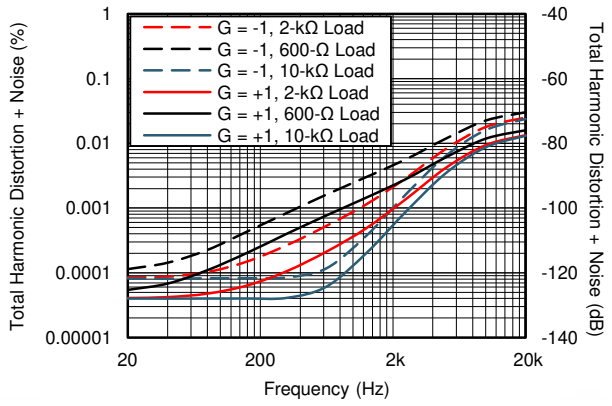
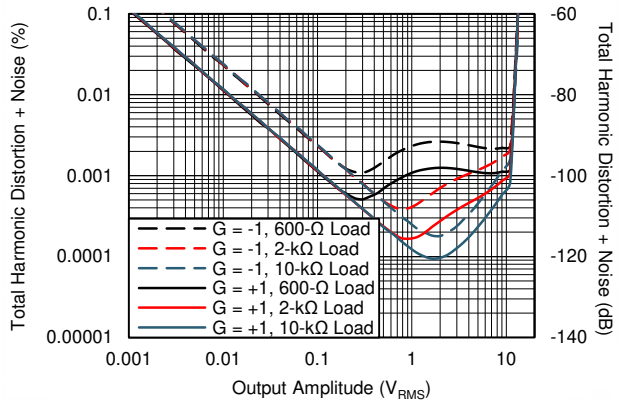


图 19. Input Voltage Noise Spectral Density vs Frequency



V_{OUT} = 3.5 V_{RMS} BW = 90 kHz

图 20. THD+N Ratio vs Frequency



f = 1 kHz BW = 90 kHz

图 21. THD+N vs Output Amplitude

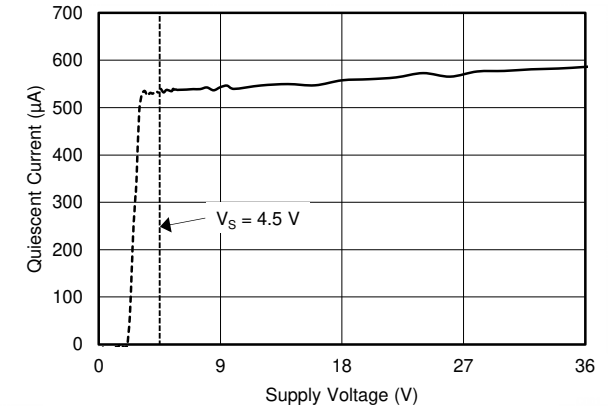


图 22. Quiescent Current vs Supply Voltage

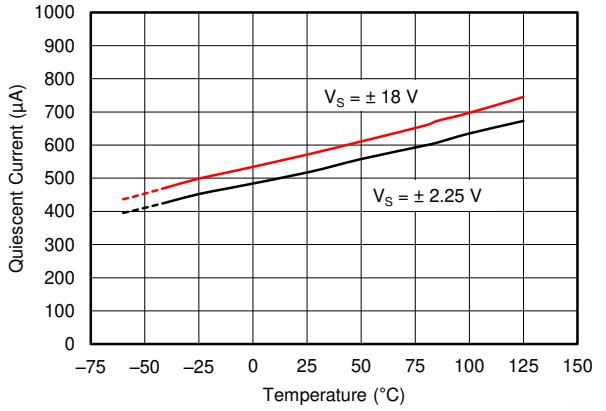


图 23. Quiescent Current vs Temperature

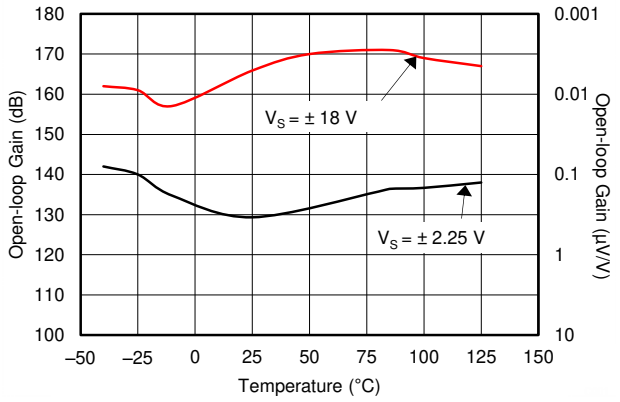


图 24. Open-Loop Gain vs Temperature (With 10-kΩ Load)

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Typical Characteristics (接下页)

at T_A = 25°C, V_S = ±18 V, V_{CM} = V_S / 2, R_{LOAD} = 10 kΩ connected to V_S / 2, and C_L = 100 pF (unless otherwise noted)

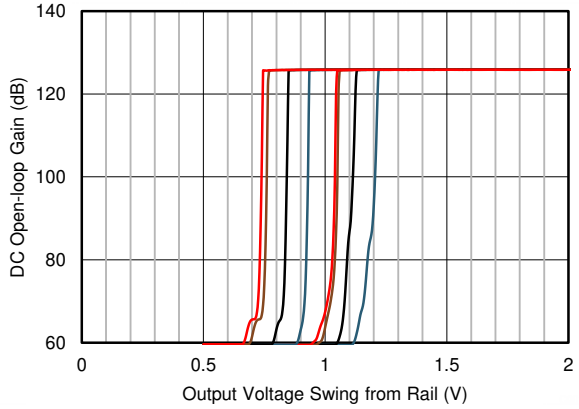


图 25. Open-Loop Gain vs Output Voltage Swing to Supply

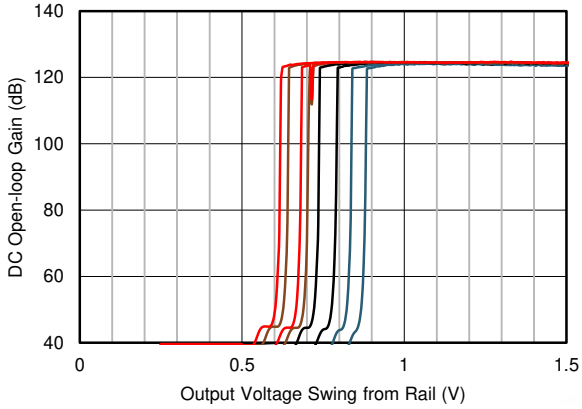


图 26. Open-Loop Gain vs Output Voltage Swing to Supply

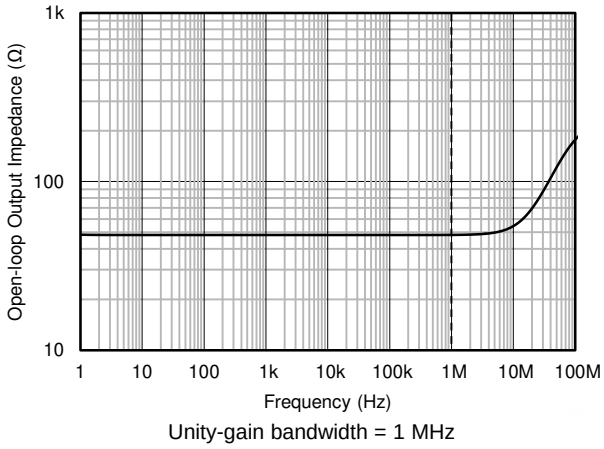


图 27. Open-Loop Output Impedance vs Frequency

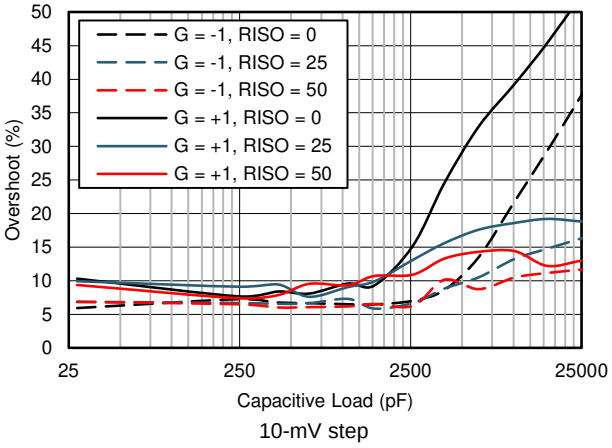


图 28. Small-Signal Overshoot vs Capacitive Load

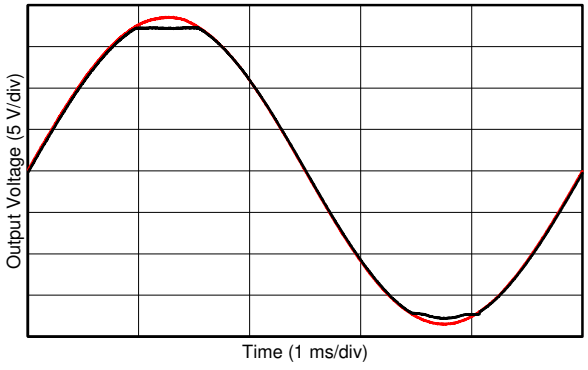


图 29. No Phase Reversal

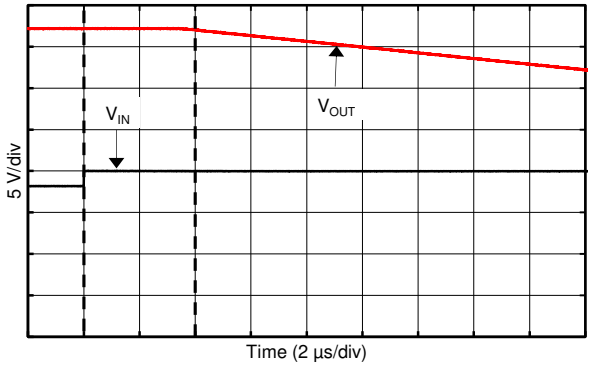


图 30. Positive Overload Recovery

Typical Characteristics (接下页)

at T_A = 25°C, V_S = ±18 V, V_{CM} = V_S / 2, R_{LOAD} = 10 kΩ connected to V_S / 2, and C_L = 100 pF (unless otherwise noted)

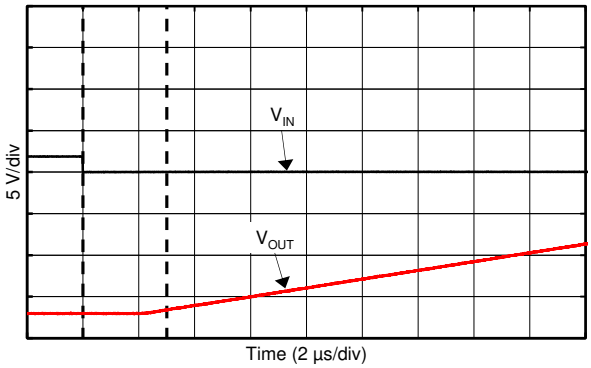
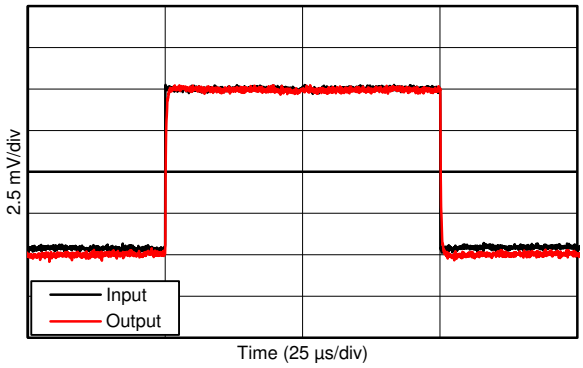
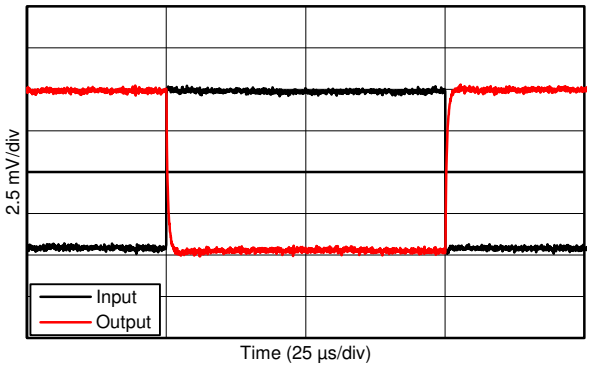


图 31. Negative Overload Recovery



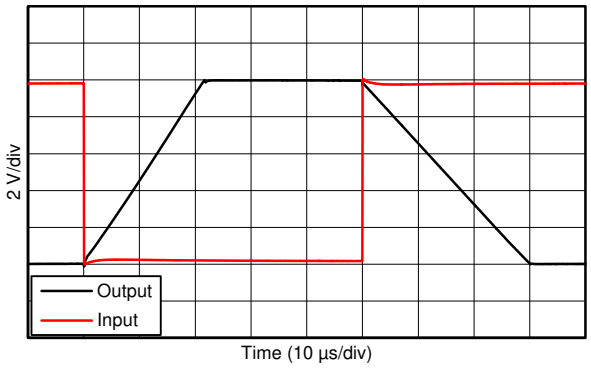
G = +1

图 32. Small-Signal Step Response (10-mV Step)



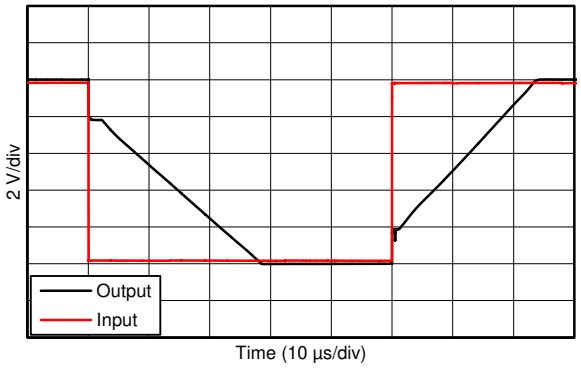
G = –1

图 33. Small-Signal Step Response (10-mV Step)



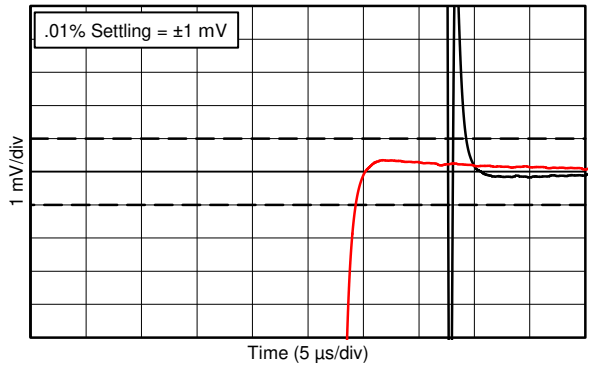
G = –1 10-V step

图 34. Large-Signal Step Response



G = +1 10-V step

图 35. Large-Signal Step Response



10-V step

图 36. Settling Time

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Typical Characteristics (接下页)

at T_A = 25°C, V_S = ±18 V, V_{CM} = V_S / 2, R_{LOAD} = 10 kΩ connected to V_S / 2, and C_L = 100 pF (unless otherwise noted)

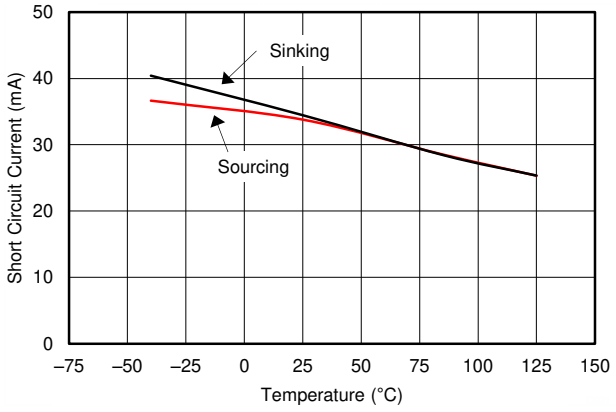


图 37. Short-Circuit Current vs Temperature

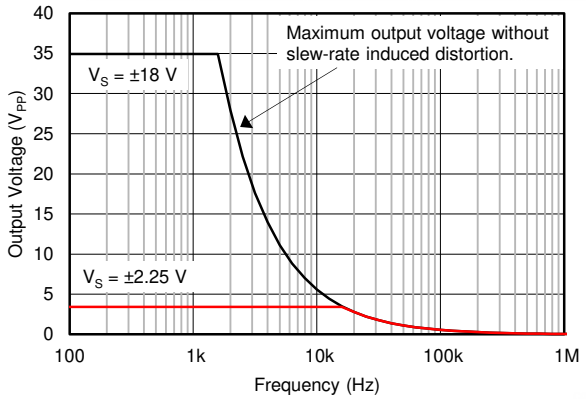
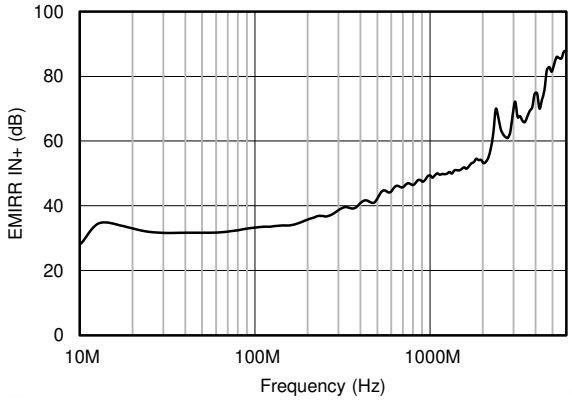


图 38. Maximum Output Voltage Amplitude vs Frequency



P_{RF} = –10 dBm

图 39. EMIRR vs Frequency

7 Detailed Description

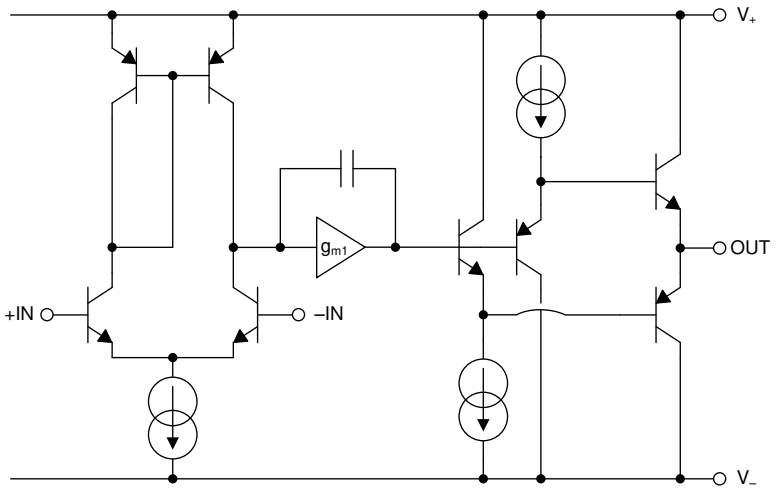
7.1 Overview

The OPA202, OPA2202, and OPA4202 (OPAx202) family of devices is a series of low-power, super-beta, bipolar junction transistor (super-β BJT), input amplifiers that features superior drift performance and low input bias current. The low output impedance and heavy capacitive load drive abilities allow designers to interface to modern, fast-acquisition, precision analog-to-digital converters (ADCs) and buffer precision voltage references and drive power supply decoupling capacitors. The OPAx202 achieve a 1-MHz gain-bandwidth product and a 0.35-V/μs slew rate, and consumes only 580 μA (typical) of quiescent current, making the devices a great choice for low-power applications. These devices operate on a single 4.5-V to 36-V supply, or dual ±2.25-V to ±18-V supplies.

All versions are fully specified from –40°C to +105°C for use in the most challenging environments. The single-channel OPA202 is available in 8-pin SOIC, 8-pin VSSOP, and 5-pin SOT-23 packages. The dual-channel OPA2202 is available in an 8-pin VSSOP package. The quad-channel OPA4202 is available in a 14-pin SOIC package.

The *Functional Block Diagram* shows the simplified diagram of the OPAx202.

7.2 Functional Block Diagram



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7.3 Feature Description

7.3.1 Capacitive Load and Stability

The dynamic characteristics of the OPAx202 are optimized for commonly encountered gains, loads, and operating conditions. The OPAx202 feature a patented output stage capable of driving large capacitive loads. In a unity-gain configuration, the series is capable of directly driving to 25 nF of pure capacitive load. Increase the gain to enhance the ability of the devices to drive greater capacitive loads. The particular op amp circuit configuration, layout, gain, and output loading are some of the factors to consider when establishing whether an amplifier is stable in operation.

The combination of low closed-loop gain and high capacitive loads decreases the phase margin of the amplifier, and can lead to gain peaking or oscillations. As a result, heavier capacitive loads must be isolated from the output. Add a small resistor (R_{OUT} equal to 50 Ω, for example) in series with the output to achieve isolation. 图 40 shows the effects on small-signal overshoot for several capacitive loads and combinations of isolation resistance. See the *Feedback Plots Define Op Amp AC Performance* application bulletin for details of analysis techniques and application circuits, available for download from the www.TI.com. By using isolation resistors, driving capacitive loads of 100 nF and beyond is possible.

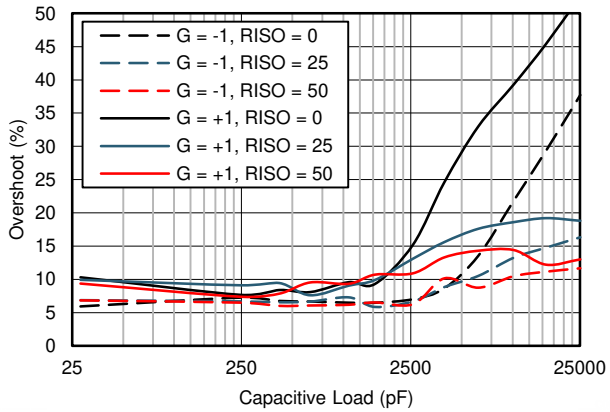

图 40. Small-Signal Overshoot vs Capacitive Load (10-mV Output Step)

Feature Description (接下页)

For additional drive capability in unity-gain configurations, insert a small (10 Ω to 20 Ω) resistor (R_{ISO}) in series with the output to improve capacitive load drive, as shown in 图 41. This resistor reduces ringing and maintains dc performance for purely capacitive loads. However, if a resistive load is in parallel with the capacitive load, then a voltage divider is created, which introduces a gain error at the output and reduces the output swing. The error is proportional to the ratio R_{ISO} / R_L, and is generally negligible at low output levels. A high capacitive load drive makes the OPAx202 a great choice for applications such as reference buffers, MOSFET gate drives, and cable-shield drives. The circuit shown in 图 41 uses an isolation resistor (R_{ISO}) to stabilize the output of an op amp. R_{ISO} modifies the open-loop gain of the system for increased phase margin. 表 2 lists the results using the OPAx202. For additional information on techniques to optimize and design using this circuit, TI Precision Design TIPD128 details complete design goals, simulation, and test results.

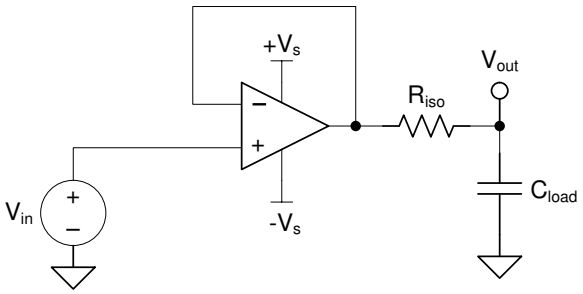

图 41. Extending Capacitive Load Drive With the OPAx202

表 2. OPAx202 Capacitive Load Drive Solution Using Isolation Resistor Measured Results

PARAMETER	MEASURED OVERSHOOT (%)					
	INVERTING CONFIGURATION			NONINVERTING CONFIGURATION		
C_{LOAD} (pF)	R_{ISO} = 0 Ω	R_{ISO} = 25 Ω	R_{ISO} = 50 Ω	R_{ISO} = 0 Ω	R_{ISO} = 25 Ω	R_{ISO} = 50 Ω
31	8.6	6.6	6.6	9.3	9	9.4
251	6.7	6.4	6.7	8.9	8.9	8.9
421	6.4	6.3	6.6	8.8	8.8	8.7
641	6.7	6.3	6.5	8.1	8.8	8.5
1079	6.1	6.1	6.4	8.6	8.7	9.8
1539	6.4	6.3	6.1	8.9	10.3	10.1
2579	6.1	6.3	6.9	16	13.3	12
3949	8.1	7.9	8.3	25	16	14.1
6269	14.9	10.8	9.9	33.1	18.1	14.5
10139	21.8	13.5	10.8	40.2	19.1	15.4
15729	29.4	15.2	11.6	46.2	19.6	14.5
25069	37	16.5	12.3	52.6	19.2	13.9

For step-by-step design procedure, circuit schematics, bill of materials, printed circuit board (PCB) files, simulation results, and test results, see TIPD128, *Capacitive Load Drive Solution Using an Isolation Resistor* verified reference design.

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7.3.2 Output Current Limit

The output current of the OPAx202 is limited by internal circuitry to ±35 mA (sinking or sourcing) to protect the device if the output is accidentally shorted. This short-circuit current depends on temperature, as 图 37 shows.

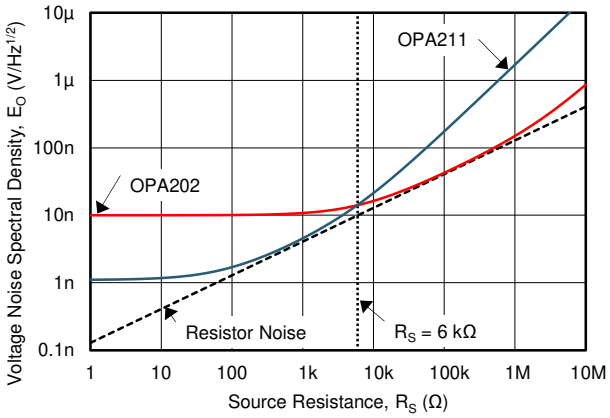
7.3.3 Noise Performance

图 42 shows the total circuit noise for varying source impedances with the operational amplifier in a unity-gain configuration (with no feedback resistor network and therefore no additional noise contributions). The OPAx202 and OPA211 are shown with total circuit noise calculated. The op amp itself contributes a voltage noise component and a current noise component. The voltage noise is commonly modeled as a time-varying component of the offset voltage. The current noise is modeled as the time-varying component of the input bias current and reacts with the source resistance to create a voltage component of noise. Therefore, the lowest noise op amp for a given application depends on the source impedance. For low source impedance, current noise is negligible and voltage noise dominates. The OPAx202 have both low voltage noise and low current noise because of the super-beta bipolar junction transistor (super-β BJT) input of the op amp. As a result, the current noise contribution of the OPAx202 is negligible for most practical source impedances, which makes the series the better choice for applications with high source impedance.

The equation in 图 42 shows the calculation of the total circuit noise with these parameters:

- e_n = voltage noise
- I_n = current noise
- R_S = source impedance
- k = Boltzmann's constant = 1.38×10^{-23} J/K
- T = temperature in kelvins (K)

For more details on calculating noise, see *Basic Noise Calculations*.



NOTE: For source resistances (R_S) greater than 6 kΩ, the OPAx202 is a lower-noise option compared to the OPA211, as shown in 图 42.

图 42. Noise Performance of the OPAx202 vs the OPA211 in a Unity-Gain Buffer Configuration

7.3.4 Phase-Reversal Protection

The OPAx202 family has internal phase-reversal protection. Many FET- and bipolar-input op amps exhibit a phase reversal when the input is driven beyond its linear common-mode range. This condition is most often encountered in noninverting circuits when the input is driven beyond the specified common-mode voltage range, causing the output to reverse into the opposite rail. The input circuitry of the OPAx202 prevents phase reversal with excessive common-mode voltage; instead, the output limits into the appropriate rail (see 图 29).

7.3.5 Thermal Protection

The OPAx202 family of op amps is capable of driving 2-kΩ loads with power-supply voltages of up to ±18 V across the specified temperature range. In a single-supply configuration, where the load is connected to the negative supply voltage, the minimum load resistance is 1.1 kΩ at a supply voltage of 36 V. For lower supply voltages (either single-supply or symmetrical supplies), a lower load resistance may be used as long as the output current does not exceed 35 mA; otherwise, the device short-circuit current protection circuit may activate.

Internal power dissipation increases when operating at high supply voltages. Copper leadframe construction used in the OPAx202 devices improves heat dissipation. Printed-circuit-board (PCB) layout helps reduce a possible increase in junction temperature. Wide copper traces help dissipate the heat by acting as an additional heat sink. An increase in temperature is further minimized by soldering the devices directly to the PCB rather than using a socket.

Although the output current is limited by internal protection circuitry, accidental shorting of one or more output channels of a device can result in excessive heating. For instance, when an output is shorted to midsupply, the typical short-circuit current of 35 mA leads to an internal power dissipation of over 600 mW at a supply of ±18 V.

To prevent excessive heating, the OPAx202 have an internal thermal shutdown circuit that shuts down the device if the die temperature exceeds approximately 135°C. When this thermal shutdown circuit activates, a built-in hysteresis of 10°C makes sure that the die temperature drops to approximately 125°C before the device switches on again. Additional consideration must be given to the combination of maximum operating voltage, maximum operating temperature, load, and package type.

7.3.6 Electrical Overstress

Designers often ask questions about the capability of an operational amplifier to withstand electrical overstress. These questions tend to focus on the device inputs, but may involve the supply voltage pins or even the output pin. Each of these different pin functions have electrical stress limits determined by the voltage breakdown characteristics of the particular semiconductor fabrication process and specific circuits connected to the pin. Additionally, internal electrostatic discharge (ESD) protection is built into these circuits to protect them from accidental ESD events both before and during product assembly.

It is helpful to have a good understanding of this basic ESD circuitry and the relevance to an electrical overstress event. See 图 43 for an illustration of the ESD circuits contained in the OPAx202 (indicated by the dashed line area). The ESD protection circuitry involves several current-steering diodes connected from the input and output pins and routed back to the internal power-supply lines, where they meet at an absorption device internal to the operational amplifier. This protection circuitry is intended to remain inactive during normal circuit operation.

An ESD event produces a short duration, high-voltage pulse that is transformed into a short duration, high-current pulse as the pulse discharges through a semiconductor device. The ESD protection circuits are designed to provide a current path around the operational amplifier core to protect the core from damage. The energy absorbed by the protection circuitry is then dissipated as heat.

When an ESD voltage develops across two or more of the amplifier device pins, current flows through one or more of the steering diodes. Depending on the path that the current takes, the absorption device may activate. The absorption device has a trigger, or threshold voltage, that is above the normal operating voltage of the OPAx202 but below the device breakdown voltage level. Once this threshold is exceeded, the absorption device quickly activates and clamps the voltage across the supply rails to a safe level.

When the operational amplifier connects into a circuit (such as the one 图 43 shows), the ESD protection components are intended to remain inactive and not become involved in the application circuit operation. However, circumstances may arise where an applied voltage exceeds the operating voltage range of a given pin. If this condition occurs, there is a risk that some of the internal ESD protection circuits may be biased on and conduct current. Any such current flow occurs through steering diode paths and rarely involves the absorption device.

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图 43 shows a specific example where the input voltage, V_{IN}, exceeds the positive supply voltage ($+V_S$) by 500 mV or more. Much of what happens in the circuit depends on the supply characteristics. If $+V_S$ can sink the current, one of the upper input steering diodes conducts and directs current to $+V_S$. Excessively high current levels can flow with increasingly higher V_{IN}. As a result, the data sheet specifications recommend that applications limit the input current to 10 mA.

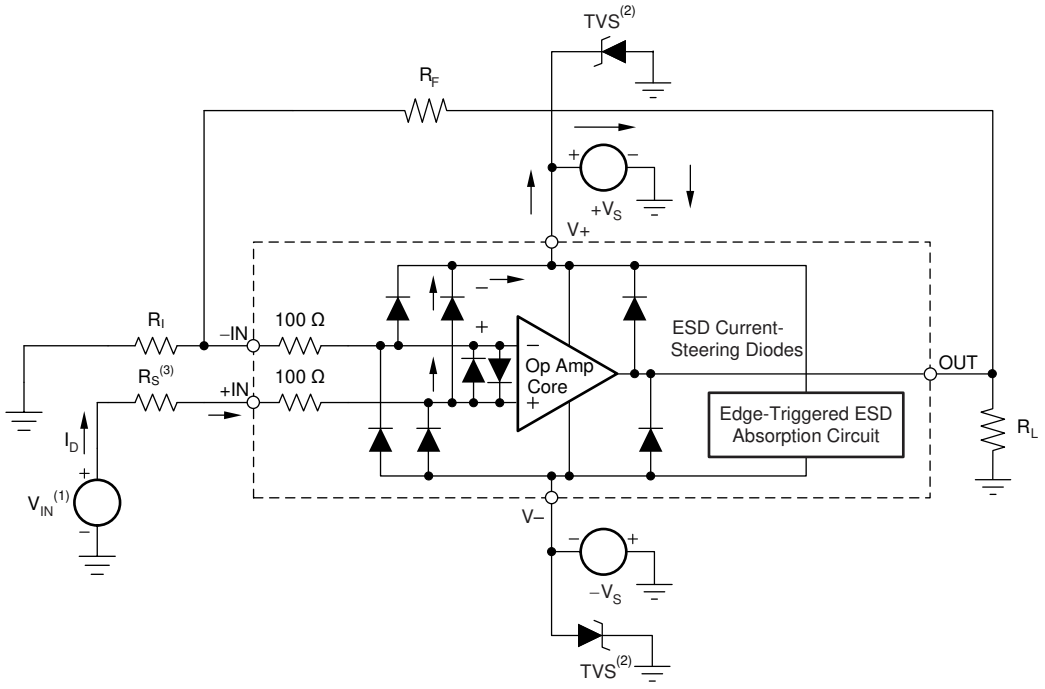
If the supply is not capable of sinking the current, V_{IN} may begin sourcing current to the operational amplifier, and then take over as the source of positive supply voltage. The danger in this case is that the voltage can rise to levels that exceed the operational amplifier absolute maximum ratings.

Another common question involves what happens to the amplifier if an input signal is applied to the input while the power supplies $+V_S$ or $-V_S$ are at 0 V.

It depends on the supply characteristic while at 0 V, or at a level below the input signal amplitude. If the supplies appear as high impedance, then the operational amplifier supply current may be supplied by the input source through the current steering diodes. This state is not a normal bias condition; the amplifier most likely does not operate normally. If the supplies are low impedance, then the current through the steering diodes can become quite high. The current level depends on the ability of the input source to deliver current, and any resistance in the input path.

If there is an uncertainty about the ability of the supply to absorb this current, external Zener diodes may be added to the supply pins as shown in 图 43. The Zener voltage must be selected such that the diode does not turn on during normal operation.

However, the Zener voltage must be low enough so that the Zener diode conducts if the supply pin rises above the safe operating supply voltage level.



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(1) $V_{IN} = +V_S + 500$ mV.

(2) TVS: $+V_{S(max)} > V_{TVSBR\ (Min)} > +V_S$

(3) Suggested value is approximately 5 kΩ in overvoltage conditions.

图 43. Equivalent Internal ESD Circuitry in a Typical Application Circuit

7.3.7 EMI Rejection

The electromagnetic interference (EMI) rejection ratio, or EMIRR, describes the EMI immunity of operational amplifiers. An adverse effect that is common to many op amps is a change in the offset voltage as a result of RF signal rectification. An op amp that is more efficient at rejecting this change in offset as a result of EMI has a higher EMIRR and is quantified by a decibel value. Measuring EMIRR is performed in many ways, but this section provides the EMIRR IN+, which specifically describes the EMIRR performance when the RF signal is applied to the noninverting input pin of the op amp. In general, only the noninverting input is tested for EMIRR for the following three reasons:

- Op amp input pins are known to be the most sensitive to EMI, and typically rectify RF signals better than the supply or output pins.
- The noninverting and inverting op amp inputs have symmetrical physical layouts and exhibit matching EMIRR performance
- EMIRR is easier to measure on noninverting pins than on other pins because the noninverting input pin can be isolated on a PCB. This isolation allows the RF signal to be applied directly to the noninverting input pin with no complex interactions from other components or connecting PCB traces.

  High-frequency signals conducted or radiated to any pin of the operational amplifier may result in adverse effects, as the amplifier does not have sufficient loop gain to correct for signals with spectral content outside the bandwidth. Conducted or radiated EMI on inputs, power supply, or output may result in unexpected DC offsets, transient voltages, or other unknown behavior. Take care to properly shield and isolate sensitive analog nodes from noisy radio signals and digital clocks and interfaces. shows the effect of conducted EMI to the power supplies on the input offset voltage of OPAx202.

  The EMIRR IN+ of the OPAx202 is plotted versus frequency, as shown in 图 44. If available, any dual and quad op-amp device versions have similar EMIRR IN+ performance. The OPAx202 unity-gain bandwidth is 1 MHz. EMIRR performance less than this frequency denotes interfering signals that fall within the op-amp bandwidth.

See the *EMI Rejection Ratio of Operational Amplifiers* application report, available for download from www.ti.com.

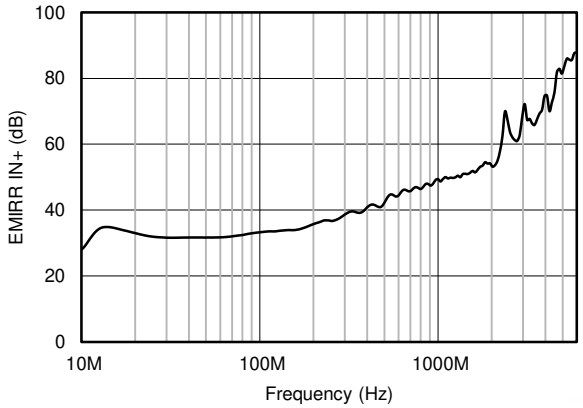

图 44. OPAx202 EMIRR IN+

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表 3 lists the EMIRR IN+ values for the OPAx202 at particular frequencies commonly encountered in real-world applications. 表 3 lists applications that may be centered on or operated near the particular frequency shown. This information may be of special interest to designers working with these types of applications, or working in other fields likely to encounter RF interference from broad sources, such as the industrial, scientific, and medical (ISM) radio band.

表 3. OPAx202 EMIRR IN+ for Frequencies of Interest

FREQUENCY	APPLICATION OR ALLOCATION	EMIRR IN+
400 MHz	Mobile radio, mobile satellite, space operation, weather, radar, ultra-high frequency (UHF) applications	41 dB
900 MHz	Global system for mobile communications (GSM) applications, radio communication, navigation, GPS (to 1.6 GHz), GSM, aeronautical mobile, UHF applications	47 dB
1.8 GHz	GSM applications, mobile personal communications, broadband, satellite, L-band (1 GHz to 2 GHz)	54 dB
2.4 GHz	802.11b, 802.11g, 802.11n, Bluetooth®, mobile personal communications, industrial, scientific and medical (ISM) radio band, amateur radio and satellite, S-band (2 GHz to 4 GHz)	67 dB
3.6 GHz	Radiolocation, aero communication and navigation, satellite, mobile, S-band	67 dB
5 GHz	802.11a, 802.11n, aero communication and navigation, mobile communication, space and satellite operation, C-band (4 GHz to 8 GHz)	81 dB

7.3.8 EMIRR +IN Test Configuration

图 45 shows the circuit configuration for testing the EMIRR IN+. An RF source is connected to the op amp noninverting input pin using a transmission line. The op amp is configured in a unity-gain buffer topology with the output connected to a low-pass filter (LPF) and a digital multimeter (DMM). A large impedance mismatch at the op amp input causes a voltage reflection; however, this effect is characterized and accounted for when determining the EMIRR IN+. The resulting DC offset voltage is sampled and measured by the multimeter. The LPF isolates the multimeter from residual RF signals that may interfere with multimeter accuracy.

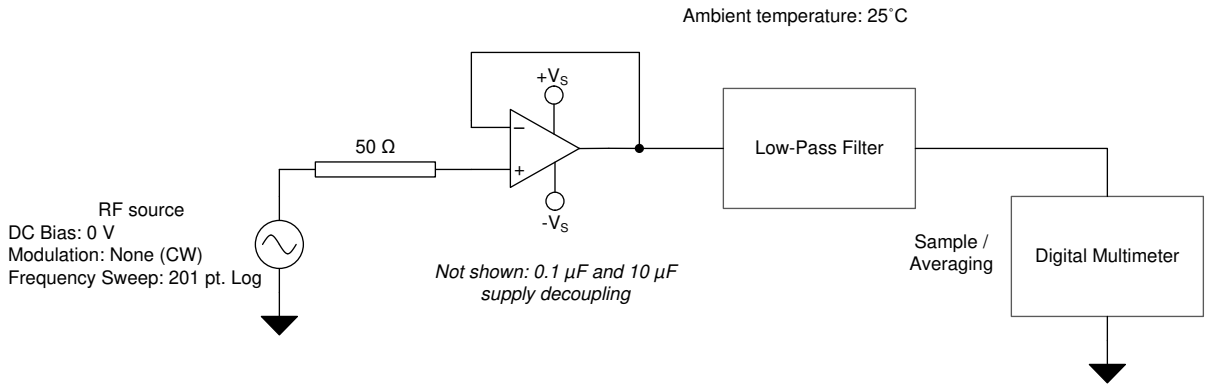

图 45. EMIRR +IN Test Configuration

7.4 Device Functional Modes

The OPAx202 have a single functional mode and are operational when the power-supply voltage is greater than 4.5 V (±2.25 V). The maximum power supply voltage for the OPAx202 is 36 V (±18 V).

8 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The OPA202, OPA2202, and OPA4202 (OPAx202) are unity-gain stable operational amplifiers with low noise, low input bias current, and low input offset voltage. Applications with noisy or high-impedance power supplies require decoupling capacitors placed close to the device pins. In most cases, 0.1-µF capacitors are adequate. Designers can use the low output impedance and heavy capacitive load drive abilities to interface to modern, fast-acquisition, precision analog-to-digital converters (ADCs) and buffer precision voltage references and drive power supply decoupling capacitors.

8.1.1 Basic Noise Calculations

Low-noise circuit design requires careful analysis of all noise sources. External noise sources dominates in many cases; consider the effect of source resistance on overall op amp noise performance. Total noise of the circuit is the root-sum-square combination of all noise components.

The resistive portion of the source impedance produces thermal noise proportional to the square root of the resistance. 图 42 shows this function. The source impedance is usually fixed; consequently, select the op amp and the feedback resistors to minimize the respective contributions to the total noise.

图 46 shows noninverting **(A)** and inverting **(B)** op amp circuit configurations with gain. In circuit configurations with gain, the feedback network resistors contribute noise. Typically, the current noise of the op amp reacts with the feedback resistors to create additional noise components. However, the extremely low current noise of the OPAx202 means that the current noise contribution is neglected.

The feedback resistor values are typically selected to make these noise sources negligible. Low impedance feedback resistors load the output of the amplifier. The equations for total noise are shown for both configurations.

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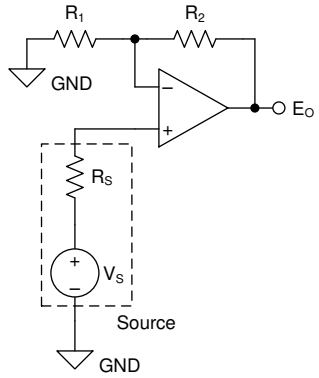
Application Information (接下页)

(A) Noise in Noninverting Gain Configuration



Noise at the output is given as E_O, where

(1) $E_O = \left(1 + \frac{R_2}{R_1}\right) \cdot \sqrt{(e_S)^2 + (e_N)^2 + \left(e_{R_1 \| R_2}\right)^2 + (i_N \cdot R_S)^2 + \left(i_N \cdot \left[\frac{R_1 \cdot R_2}{R_1 + R_2}\right]\right)^2}$ $[\,V_{RMS}\,]$

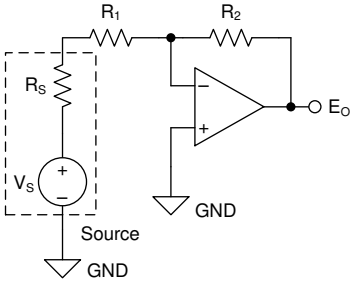
(2) $e_S = \sqrt{4 \cdot k_B \cdot T(K) \cdot R_S}$ $\left[\frac{V}{\sqrt{Hz}}\right]$ Thermal noise of R_S

(3) $e_{R_1 \| R_2} = \sqrt{4 \cdot k_B \cdot T(K) \cdot \left[\frac{R_1 \cdot R_2}{R_1 + R_2}\right]}$ $\left[\frac{V}{\sqrt{Hz}}\right]$ Thermal noise of R_1 || R_2

(4) $k_B = 1.38065 \cdot 10^{-23}$ $\left[\frac{J}{K}\right]$ Boltzmann Constant

(5) $T(K) = 237.15 + T(°C)$ $[\,K\,]$ Temperature in kelvins

(B) Noise in Inverting Gain Configuration



Noise at the output is given as E_O, where

(6) $E_O = \left(1 + \frac{R_2}{R_S + R_1}\right) \cdot \sqrt{(e_N)^2 + \left(e_{R_1 + R_S \| R_2}\right)^2 + \left(i_N \cdot \left[\frac{(R_S + R_1) \cdot R_2}{R_S + R_1 + R_2}\right]\right)^2}$ $[\,V_{RMS}\,]$

(7) $e_{R_1 + R_S \| R_2} = \sqrt{4 \cdot k_B \cdot T(K) \cdot \left[\frac{(R_S + R_1) \cdot R_2}{R_S + R_1 + R_2}\right]}$ $\left[\frac{V}{\sqrt{Hz}}\right]$ Thermal noise of (R_1 + R_S) || R_2

(8) $k_B = 1.38065 \cdot 10^{-23}$ $\left[\frac{J}{K}\right]$ Boltzmann Constant

(9) $T(K) = 237.15 + T(°C)$ $[\,K\,]$ Temperature in kelvins

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(1) e_N = the voltage noise of the amplifier = 9 nV/√Hz at 1 kHz.
(2) i_N = the current noise of the amplifier = 76 fA/√Hz at 1 kHz.
(3) For additional resources on noise calculations, visit *TI's Precision Labs*.

图 46. Noise Calculation in Gain Configurations

8.2 Typical Application

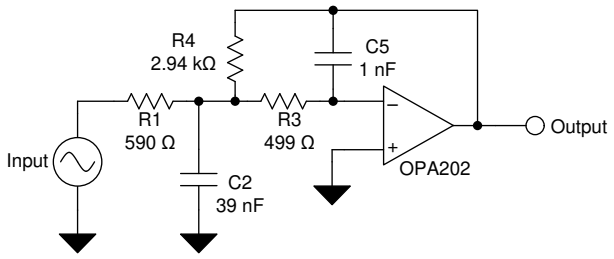

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图 47. 25-kHz, Low-Pass Filter

8.2.1 Design Requirements

Low-pass filters are used in signal processing applications to reduce noise and prevent aliasing. The OPAx202 devices are is designed to construct high-speed, high-precision active filters. 图 47 shows a second-order, low-pass filter commonly encountered in signal processing applications.

Use the following parameters for this design example:

- Gain = 5 V/V (inverting gain)
- Low-pass cutoff frequency = 25 kHz
- Second-order Chebyshev filter response with 3-dB gain peaking in the passband

8.2.2 Detailed Design Procedure

The infinite-gain multiple-feedback circuit for a low-pass network function is shown in 图 47. Use 公式 1 to calculate the voltage transfer function.

$$\frac{\text{Output}}{\text{Input}}(s) = \frac{-1/R_1R_3C_2C_5}{s^2 + (s/C_2)(1/R_1 + 1/R_3 + 1/R_4) + 1/R_3R_4C_2C_5} \tag{1}$$

This circuit produces a signal inversion. For this circuit, the gain at DC and the low-pass cutoff frequency are calculated by 公式 2:

$$\text{Gain} = \frac{R_4}{R_1}$$

$$f_C = \frac{1}{2\pi}\sqrt{(1/R_3R_4C_2C_5)} \tag{2}$$

Software tools are readily available to simplify filter design. WEBENCH® Filter Designer is a simple, powerful, and easy-to-use active filter design program. The WEBENCH® Filter Designer lets you create optimized filter designs using a selection of TI operational amplifiers and passive components from TI's vendor partners.

Available as a web based tool from the WEBENCH Design Center, WEBENCH Filter Designer allows you to design, optimize, and simulate complete multistage active filter solutions within minutes.

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Typical Application (接下页)

8.2.3 Application Curve

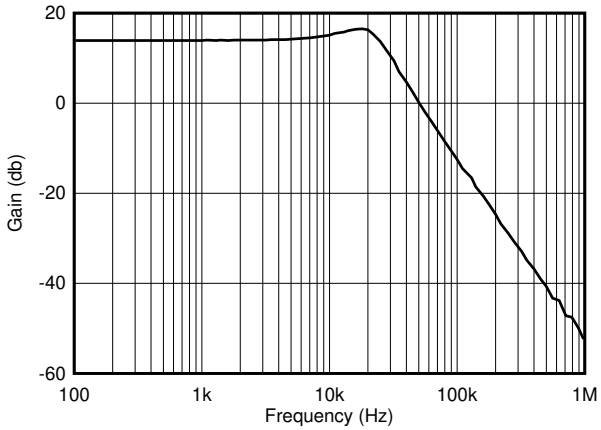

图 48. OPAx202 Second-Order, 25-kHz, Chebyshev, Low-Pass Filter

9 Power Supply Recommendations

The OPAx202 are specified for operation from 4.5 V to 36 V (±2.25 V to ±18 V); many specifications apply from –40°C to +105°C. Parameters that can exhibit significant variance with regard to operating voltage or temperature are shown in the *Typical Characteristics*.

CAUTION

Supply voltages greater than 40 V can permanently damage the device; see the *Absolute Maximum Ratings*.

Place 0.1-μF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement, see the *Layout* section.

10 Layout

10.1 Layout Guidelines

For best operational performance of the device, use good PCB layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole and the op amp itself. Bypass capacitors are used to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
  - Connect low-ESR, 0.1-µF ceramic bypass capacitors between each supply pin and ground, placed as close as possible to the device. A single bypass capacitor from V+ to ground is applicable for single-supply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically separate digital and analog grounds paying attention to the flow of the ground current. For more detailed information, see *The PCB is a component of op amp design.*
- To reduce parasitic coupling, run the input traces as far away as possible from the supply or output traces. If these traces cannot be kept separate, crossing the sensitive trace perpendicular is much better as opposed to in parallel with the noisy trace.
- Place the external components as close as possible to the device. As shown in 图 49, keeping RF and RG close to the inverting input minimizes parasitic capacitance.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.
- For best performance, TI recommends cleaning the PCB following board assembly.
- Any precision integrated circuit may experience performance shifts due to moisture ingress into the plastic package. Following any aqueous PCB cleaning process, TI recommends baking the PCB assembly to remove moisture introduced into the device packaging during the cleaning process. A low temperature, post cleaning bake at 85°C for 30 minutes is sufficient for most circumstances.

10.2 Layout Example

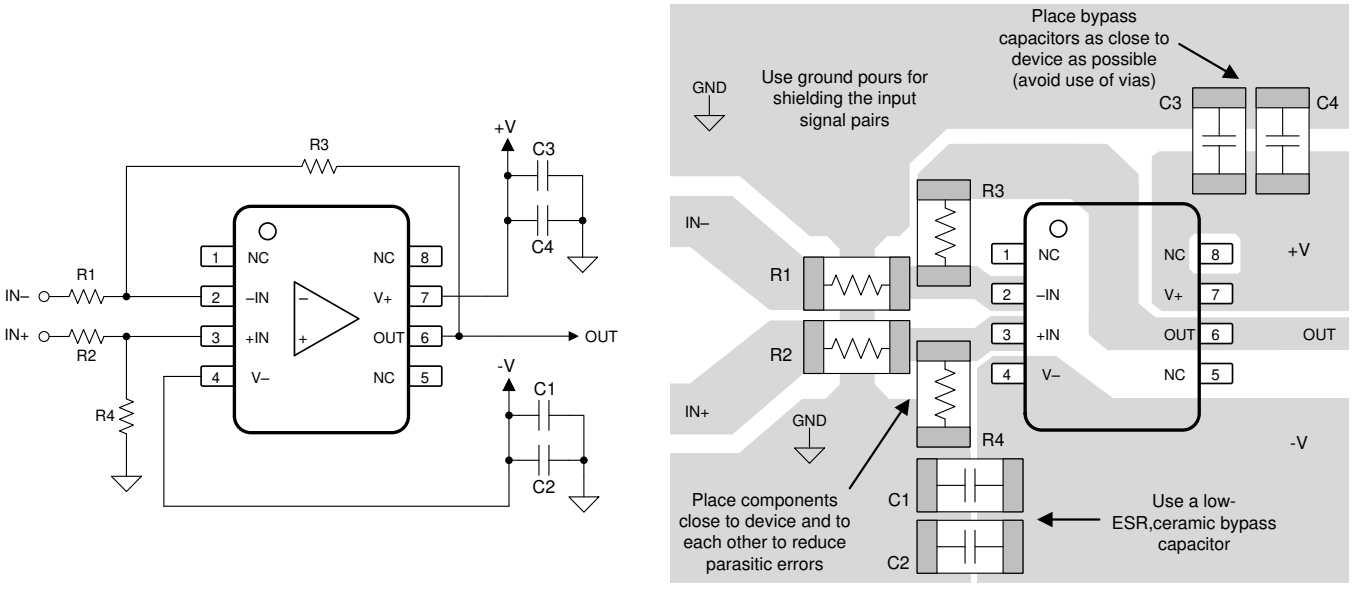

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图 49. Operational Amplifier Board Layout for Difference Amplifier Configuration

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11 器件和文档支持

11.1 器件支持

11.1.1 开发支持

11.1.1.1 TINA-TI™（免费软件下载）

TINA™是一款简单、功能强大且易于使用的电路仿真程序，此程序基于 SPICE 引擎。TINA-TI 是 TINA 软件的一款免费全功能版本，除了一系列无源和有源模型外，此版本软件还预先载入了一个宏模型库。TINA-TI 提供所有传统的 SPICE 直流、瞬态和频域分析，以及其他设计功能。

TINA-TI 可从 Analog eLab Design Center（模拟电子实验室设计中心）免费下载，它提供全面的后续处理能力，使得用户能够以多种方式形成结果。虚拟仪器提供选择输入波形和探测电路节点、电压和波形的功能，从而创建一个动态的快速入门工具。

注

这些文件需要安装 TINA 软件（由 DesignSoft™提供）或者 TINA-TI 软件。请从 TINA-TI 文件夹 中下载免费的 TINA-TI 软件。

11.1.1.2 WEBENCH 滤波器设计器工具

WEBENCH® 滤波器设计器是一款简单、功能强大且便于使用的有源滤波器设计程序。借助 WEBENCH 滤波器设计器，用户可使用精选 TI 运算放大器和 TI 供应商合作伙伴提供的无源组件来构建最佳滤波器设计方案。

11.1.1.3 TI 高精度设计

欲获取 TI 高精度设计，请访问 http://www.ti.com.cn/ww/analog/precision-designs/。TI 高精度设计是由 TI 公司高精度模拟 应用 专家创建的模拟解决方案，提供了许多实用电路的工作原理、组件选择、仿真、完整印刷电路板 (PCB) 电路原理图和布局布线、物料清单以及性能测量结果。

11.2 文档支持

11.2.1 相关文档

请参阅如下相关文档：

- 德州仪器 (TI)，*《运算放大器设计组件 PCB》*
- 德州仪器 (TI)，*《用直观方式补偿跨阻放大器》*
- 德州仪器 (TI)，*《运算放大器增益稳定性，第 3 部分：交流增益误差分析》*
- 德州仪器 (TI)，*《运算放大器增益稳定性，第 2 部分：直流增益误差分析》*
- 德州仪器 (TI)，*《在全差分有源滤波器中使用无限增益、MFB 滤波器拓扑》*
- 德州仪器 (TI)，*《运算放大器性能分析》*
- 德州仪器 (TI)，*《运算放大器的单电源运行》*
- 德州仪器 (TI)，*《放大器调优》*
- 德州仪器 (TI)，*《无铅组件涂层的储存寿命评估》*
- 德州仪器 (TI)，*《反馈曲线图定义运算放大器交流性能》*
- 德州仪器 (TI)，*《运算放大器的 EMI 抑制比》*

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11.3 相关链接

表 4 列出了快速访问链接。类别包括技术文档、支持和社区资源、工具与软件，以及立即订购快速访问。

表 4. 相关链接

器件	产品文件夹	立即订购	技术文档	工具与软件	支持和社区
OPA202	单击此处	单击此处	单击此处	单击此处	单击此处
OPA2202	单击此处	单击此处	单击此处	单击此处	单击此处
OPA4202	单击此处	单击此处	单击此处	单击此处	单击此处

11.4 接收文档更新通知

要接收文档更新通知，请导航至 ti.com. 上的器件产品文件夹。单击右上角的*通知我*进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

11.5 支持资源

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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11.6 商标

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11.7 静电放电警告

ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。 精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

11.8 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
OPA202ID	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 120	OPA202	Samples
OPA202IDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 120	1T72	Samples
OPA202IDBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 120	1T72	Samples
OPA202IDGKR	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAUAG | SN	Level-2-260C-1 YEAR	-40 to 105	1T2Q	Samples
OPA202IDGKT	ACTIVE	VSSOP	DGK	8	250	RoHS & Green	NIPDAUAG | SN	Level-2-260C-1 YEAR	-40 to 105	1T2Q	Samples
OPA202IDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 120	OPA202	Samples
OPA2202ID	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	OP2202	Samples
OPA2202IDGKR	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAUAG | SN	Level-2-260C-1 YEAR	-40 to 120	1XDQ	Samples
OPA2202IDGKT	ACTIVE	VSSOP	DGK	8	250	RoHS & Green	NIPDAUAG | SN	Level-2-260C-1 YEAR	-40 to 120	1XDQ	Samples
OPA2202IDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 150	OP2202	Samples
OPA4202ID	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	OPA4202	Samples
OPA4202IDR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	OPA4202	Samples
OPA4202IPW	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	OPA4202	Samples
OPA4202IPWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	OPA4202	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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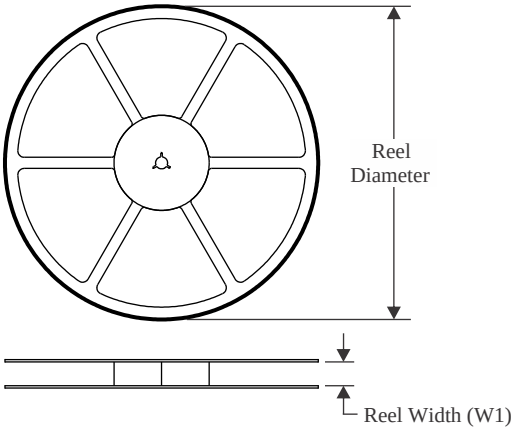
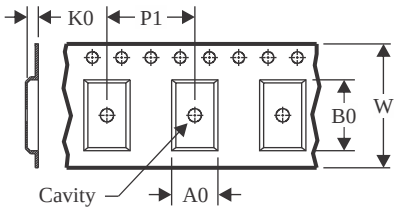
TAPE AND REEL INFORMATION

REEL DIMENSIONS

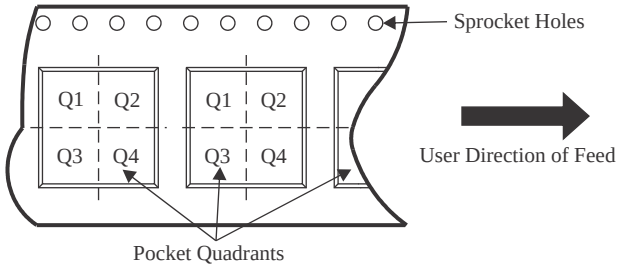


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

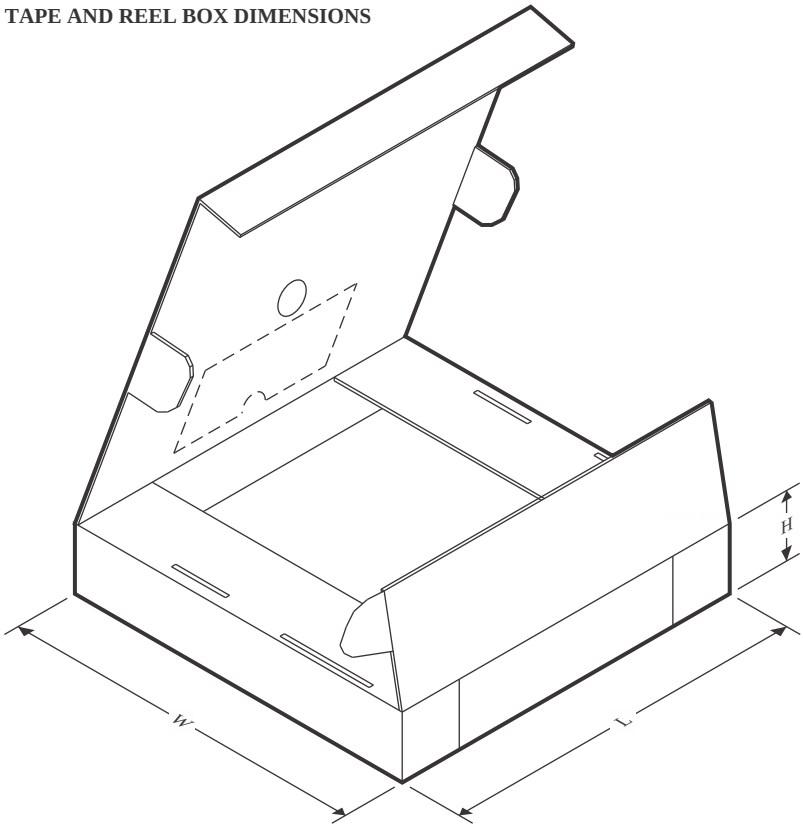
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
OPA202IDBVR	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
OPA202IDBVT	SOT-23	DBV	5	250	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
OPA202IDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
OPA202IDGKT	VSSOP	DGK	8	250	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
OPA202IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA2202IDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
OPA2202IDGKT	VSSOP	DGK	8	250	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
OPA2202IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA4202IDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
OPA4202IPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

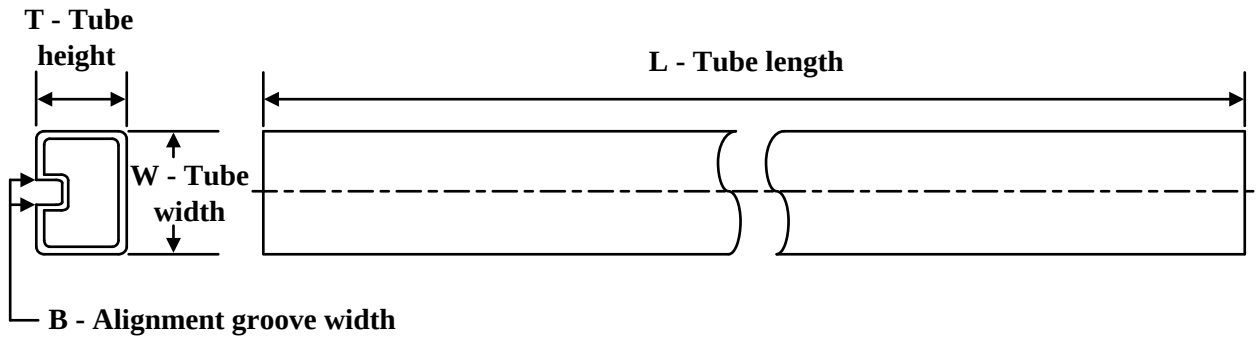
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
OPA202IDBVR	SOT-23	DBV	5	3000	213.0	191.0	35.0
OPA202IDBVT	SOT-23	DBV	5	250	213.0	191.0	35.0
OPA202IDGKR	VSSOP	DGK	8	2500	366.0	364.0	50.0
OPA202IDGKT	VSSOP	DGK	8	250	366.0	364.0	50.0
OPA202IDR	SOIC	D	8	2500	356.0	356.0	35.0
OPA2202IDGKR	VSSOP	DGK	8	2500	366.0	364.0	50.0
OPA2202IDGKT	VSSOP	DGK	8	250	366.0	364.0	50.0
OPA2202IDR	SOIC	D	8	2500	356.0	356.0	35.0
OPA4202IDR	SOIC	D	14	2500	356.0	356.0	35.0
OPA4202IPWR	TSSOP	PW	14	2000	356.0	356.0	35.0

TUBE



*All dimensions are nominal

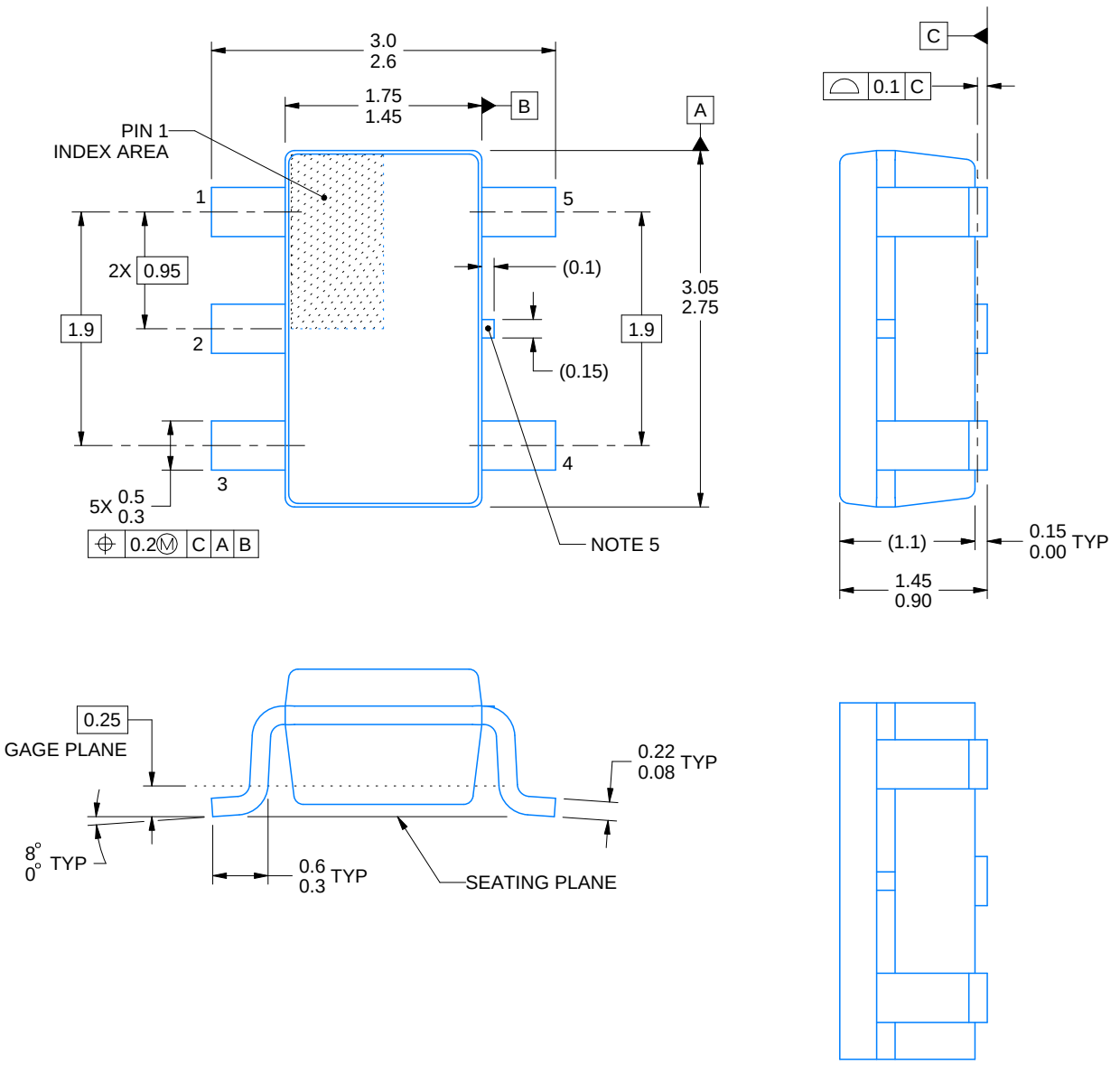
Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
OPA202ID	D	SOIC	8	75	506.6	8	3940	4.32
OPA2202ID	D	SOIC	8	75	506.6	8	3940	4.32
OPA4202ID	D	SOIC	14	50	506.6	8	3940	4.32
OPA4202IPW	PW	TSSOP	14	90	530	10.2	3600	3.5

PACKAGE OUTLINE

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR

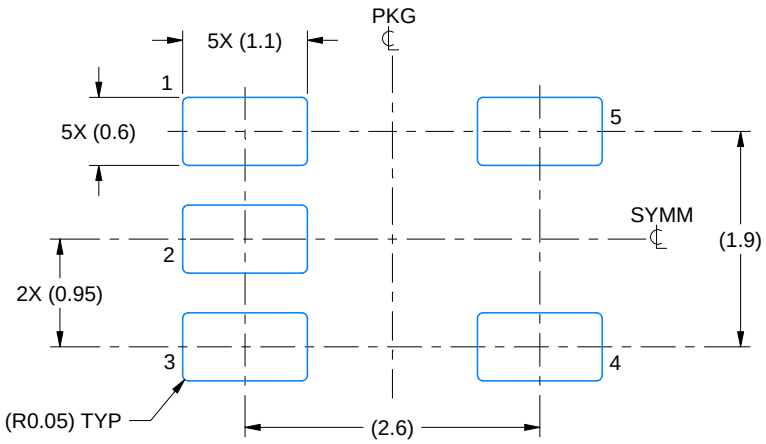


ALTERNATIVE PACKAGE SINGULATION VIEW

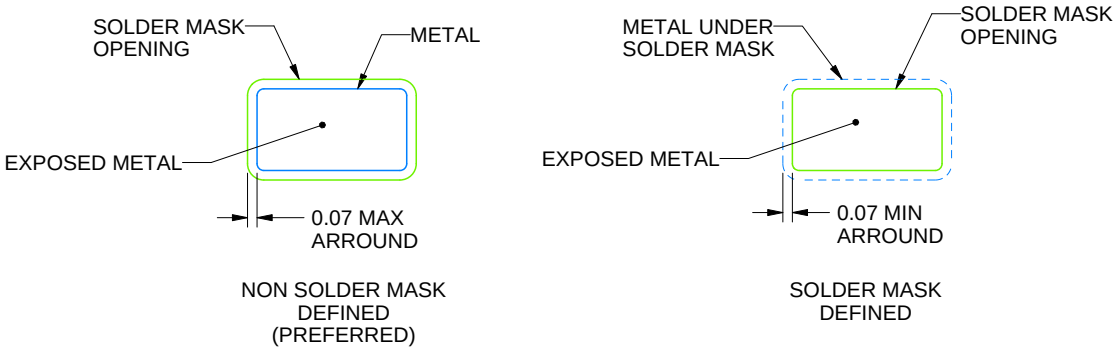
4214839/J 02/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Refernce JEDEC MO-178.
4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
5. Support pin may differ or may not be present.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X

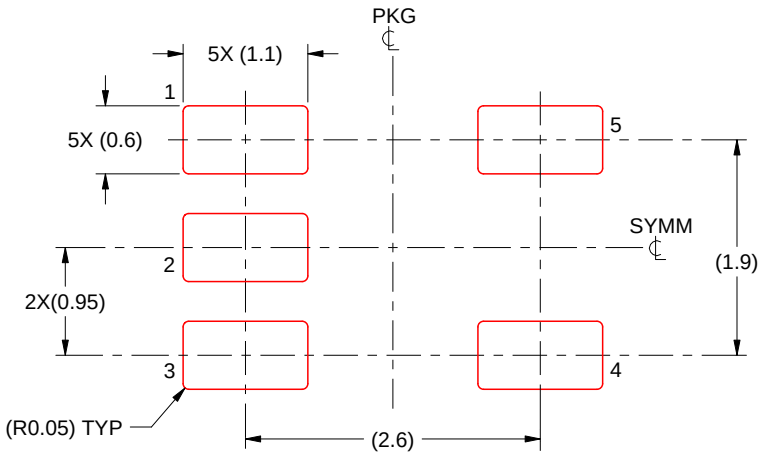


SOLDER MASK DETAILS

4214839/J 02/2024

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



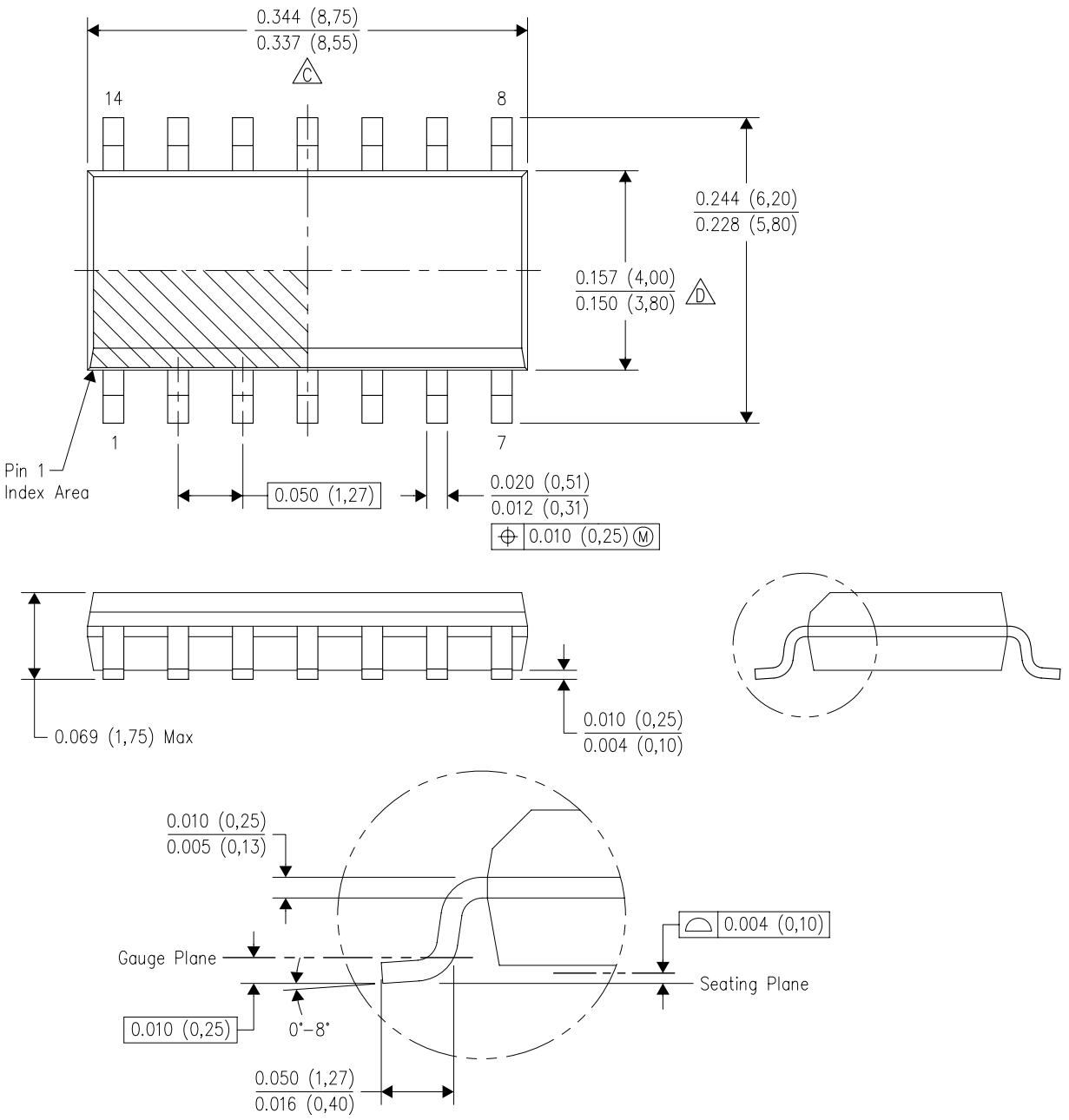
SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214839/J 02/2024

NOTES: (continued)

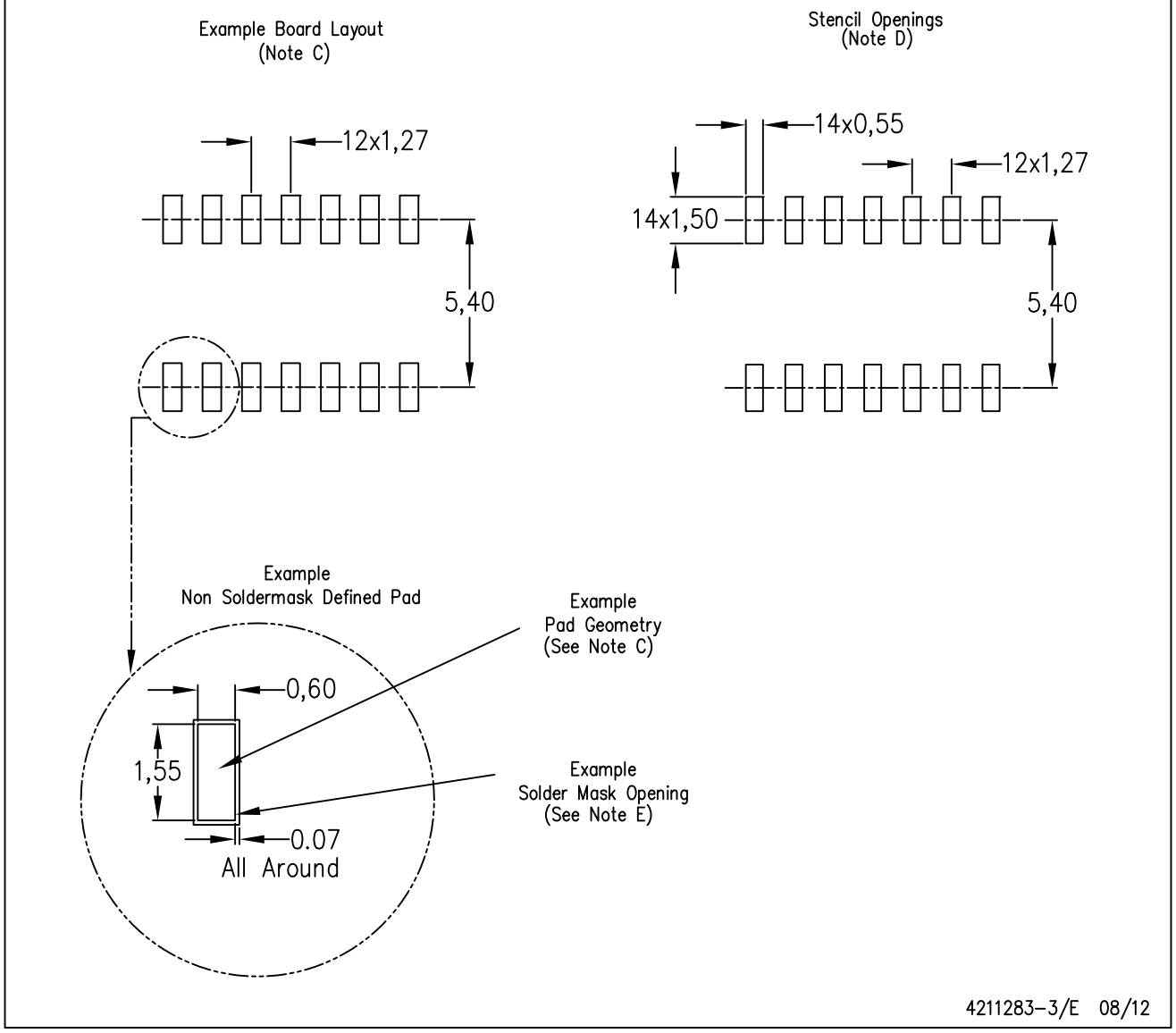
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

D (R–PDSO–G14) PLASTIC SMALL OUTLINE



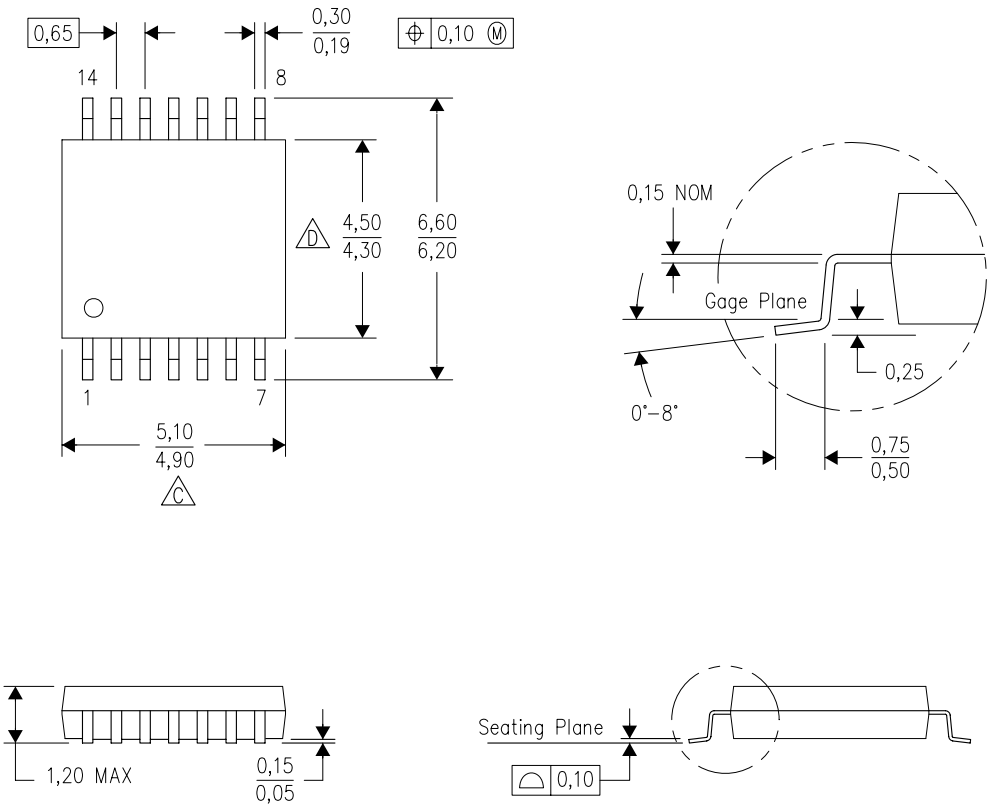
NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AB.

D (R–PDSO–G14) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

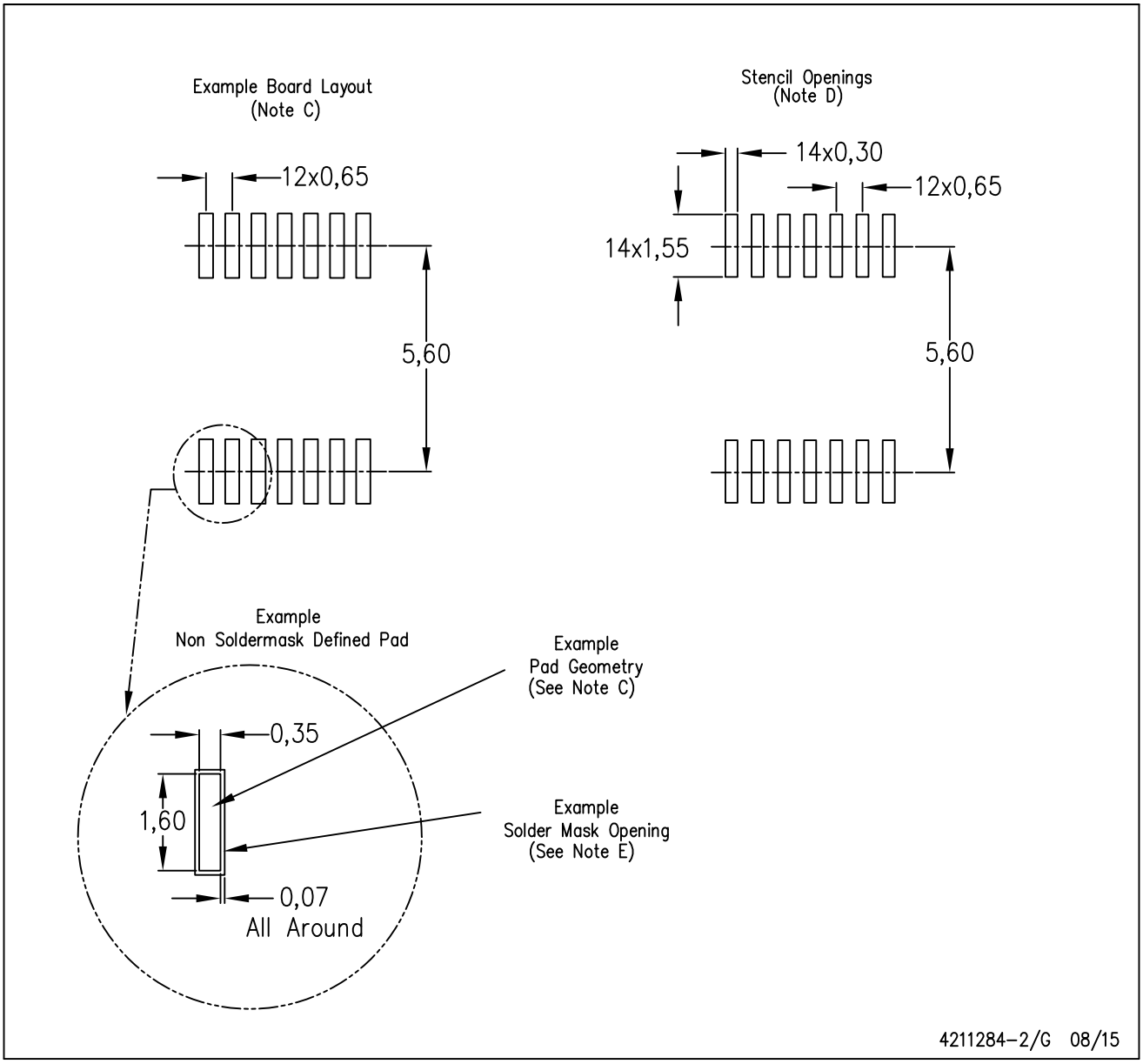
PW (R–PDSO–G14) PLASTIC SMALL OUTLINE



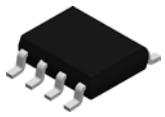
4040064–3/G 02/11

NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
E. Falls within JEDEC MO–153

PW (R–PDSO–G14) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

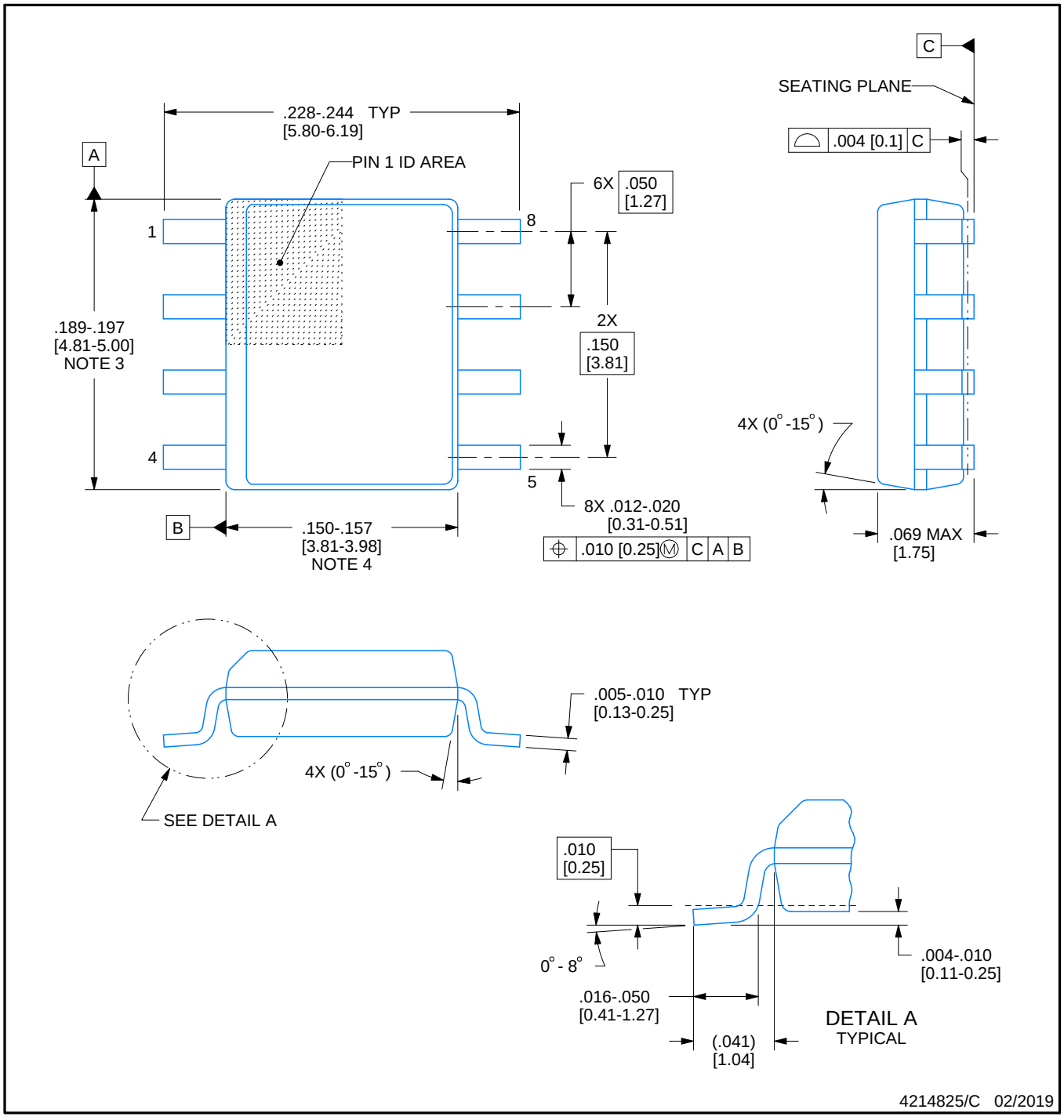


PACKAGE OUTLINE

D0008A

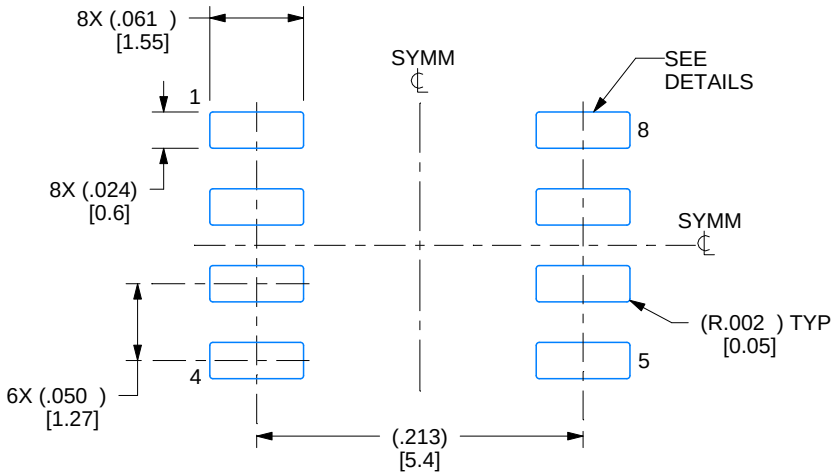
SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

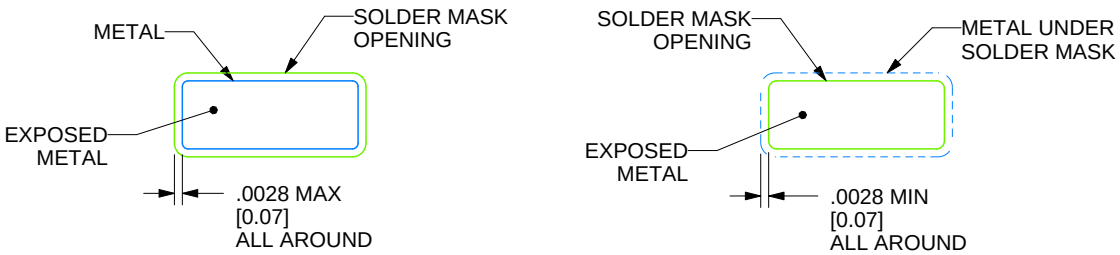


NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

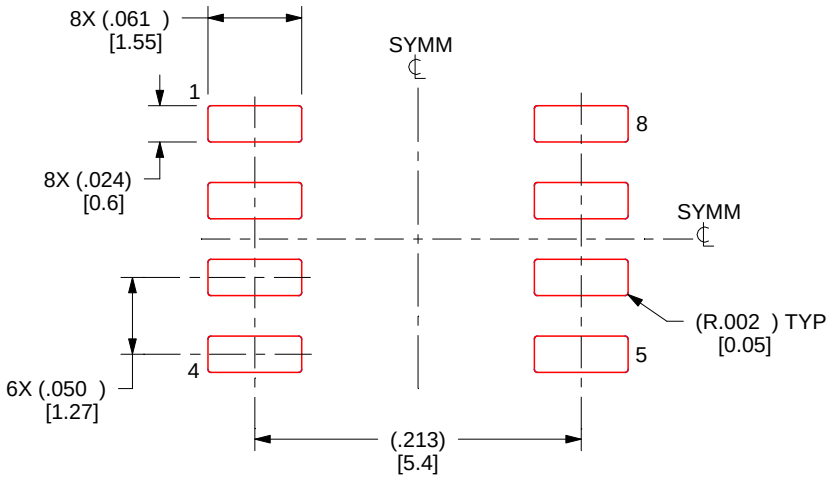
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

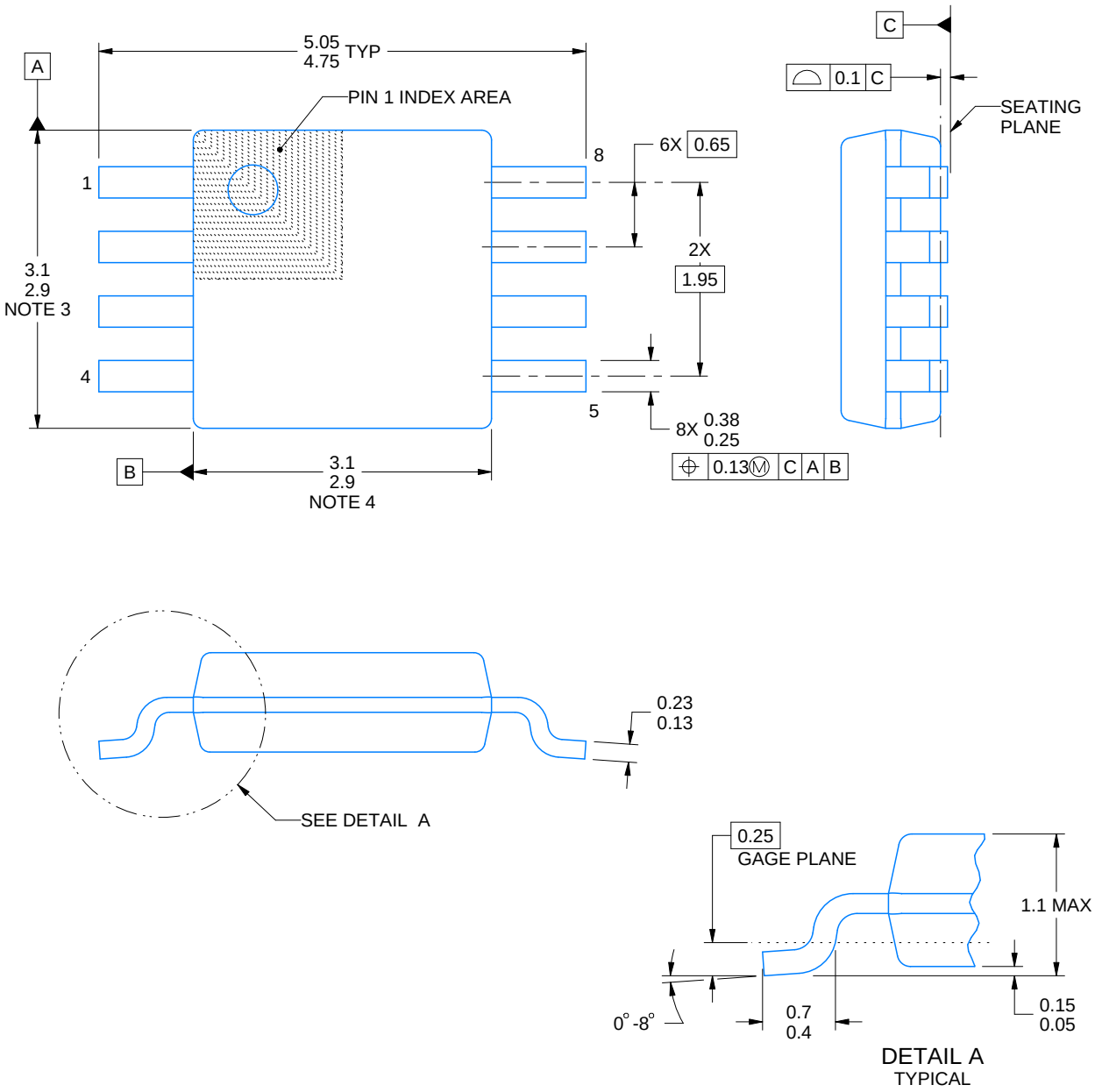
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

PACKAGE OUTLINE

DGK0008A

VSSOP - 1.1 mm max height

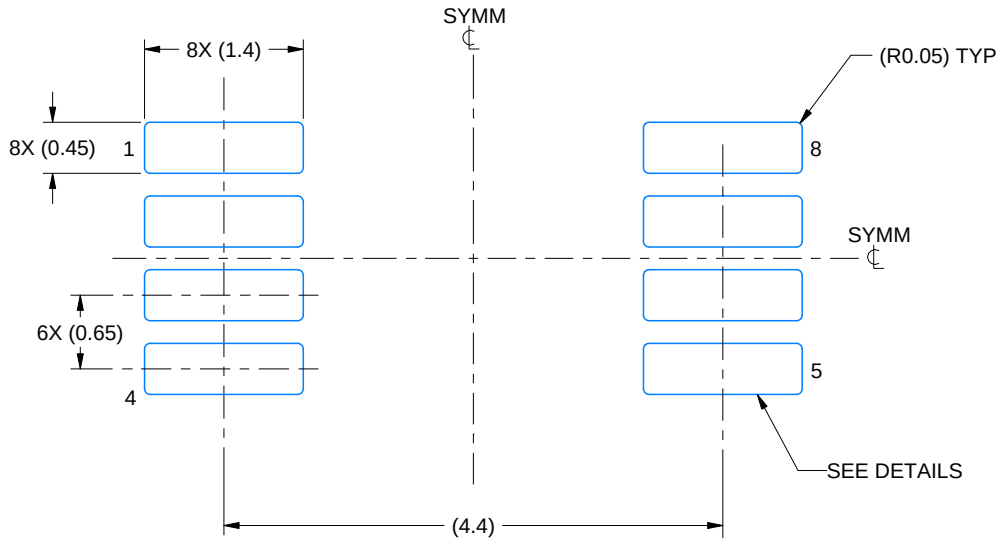
SMALL OUTLINE PACKAGE



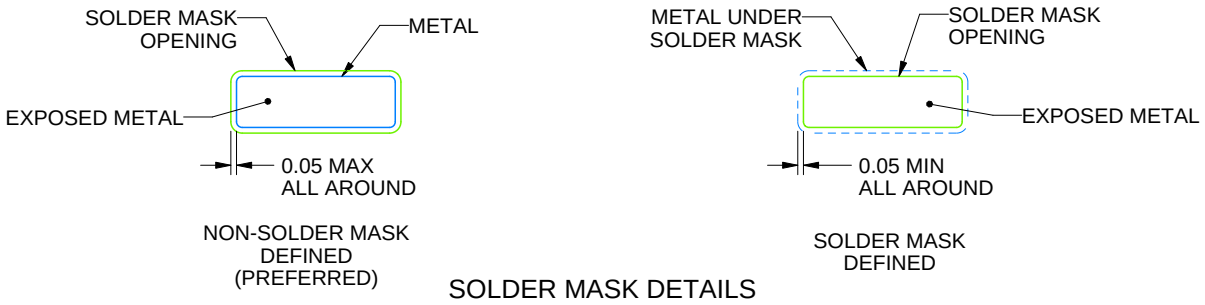
PowerPAD is a trademark of Texas Instruments.

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-187.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 15X

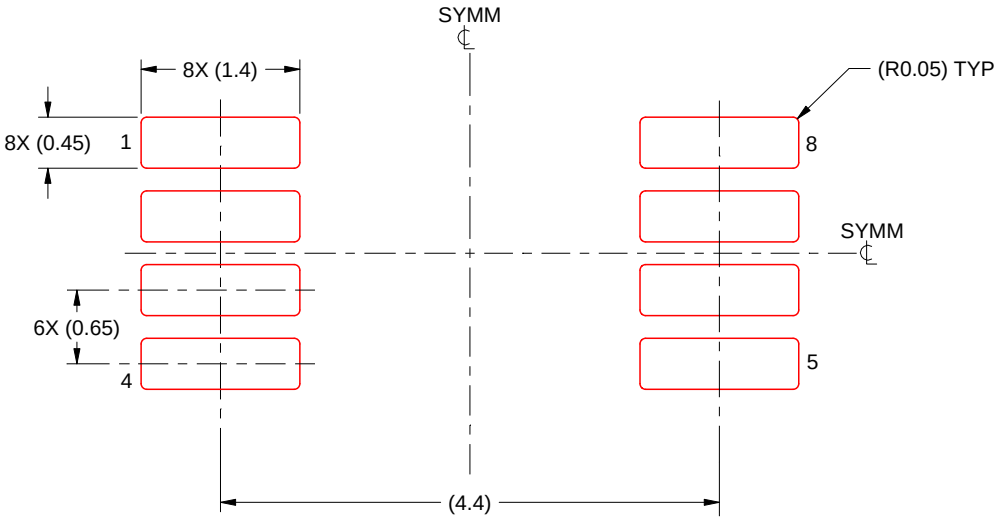


SOLDER MASK DETAILS

4214862/A 04/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
9. Size of metal pad may vary due to creepage requirement.



SOLDER PASTE EXAMPLE
SCALE: 15X

4214862/A 04/2023

NOTES: (continued)

11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
12. Board assembly site may have different recommendations for stencil design.

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